Renesas Power MOS FETs, IGBTs, Triacs, and Thyristors General Presentation

Renesas Technology www.renesas.com



Renesas Power MOS FETs, IGBTs, Triacs, and Thyristors General Presentation January 2010

Renesas Technology Corp.

Standard Product Business Group

2/2/2010 Rev.27.01

Notes regarding these materials

- 1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warranties or representations with respect to the accuracy or completeness of the information contained in this document nor grants any license to any intellectual property rights or any other rights of Renesas or any third party with respect to the information in this document.
- 2. Renesas shall have no liability for damages or infringement of any intellectual property or other rights arising out of the use of any information in this document, including, but not limited to, product data, diagrams, charts, programs, algorithms, and application circuit examples.
- 3. You should not use the products or the technology described in this document for the purpose of military applications such as the development of weapons of mass destruction or for the purpose of any other military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations.
- 4. All information included in this document such as product data, diagrams, charts, programs, algorithms, and application circuit examples, is current as of the date this document is issued. Such information, however, is subject to change without any prior notice. Before purchasing or using any Renesas products listed in this document, please confirm the latest product information with a Renesas sales office. Also, please pay regular and careful attention to additional and different information to be disclosed by Renesas such as that disclosed through our website. (http://www.renesas.com)
- 5. Renesas has used reasonable care in compiling the information included in this document, but Renesas assumes no liability whatsoever for any damages incurred as a result of errors or omissions in the information included in this document.
- 6. When using or otherwise relying on the information in this document, you should evaluate the information in light of the total system before deciding about the applicability of such information to the intended application. Renesas makes no representations, warranties or guaranties regarding the suitability of its products for any particular application and specifically disclaims any liability arising out of the application and use of the information in this document or Renesas products.
- 7. With the exception of products specified by Renesas as suitable for automobile applications, Renesas products are not designed, manufactured or tested for applications or otherwise in systems the failure or malfunction of which may cause a direct threat to human life or create a risk of human injury or which require especially high quality and reliability such as safety systems, or equipment or systems for transportation and traffic, healthcare, combustion control, aerospace and aeronautics, nuclear power, or undersea communication transmission. If you are considering the use of our products for such purposes, please contact a Renesas sales office beforehand. Renesas shall have no liability for damages arising out of the uses set forth above.
- 8. Notwithstanding the preceding paragraph, you should not use Renesas products for the purposes listed below:
 - (1) artificial life support devices or systems
 - (2) surgical implantations
 - (3) healthcare intervention (e.g., excision, administration of medication, etc.)
 - (4) any other purposes that pose a direct threat to human life
 - Renesas shall have no liability for damages arising out of the uses set forth in the above and purchasers who elect to use Renesas products in any of the foregoing applications shall indemnify and hold harmless Renesas Technology Corp., its affiliated companies and their officers, directors, and employees against any and all damages arising out of such applications.
- 9. You should use the products described herein within the range specified by Renesas, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas shall have no liability for malfunctions or damages arising out of the use of Renesas products beyond such specified ranges.
- 10. Although Renesas endeavors to improve the quality and reliability of its products, IC products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Please be sure to implement safety measures to guard against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other applicable measures. Among others, since the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or system manufactured by you.
- 11. In case Renesas products listed in this document are detached from the products to which the Renesas products are attached or affixed, the risk of accident such as swallowing by infants and small children is very high. You should implement safety measures so that Renesas products may not be easily detached from your products. Renesas shall have no liability for damages arising out of such detachment.
- 12. This document may not be reproduced or duplicated, in any form, in whole or in part, without prior written approval from Renesas.
- 13. Please contact a Renesas sales office if you have any questions regarding the information contained in this document, Renesas semiconductor products, or if you have any other inquiries.



Contents

Power MOS FETs

- Applications, Development Trends
- Low-Voltage Power MOS FETs
- 10th Generation Power MOS FETs (V_{DSS}= 30 V)
- New Products: 10th Generation + SBD (Single/Dual)
- Next Generation Products: 11th Generation Power MOS FETs
- New Products: Middle Voltage (40 V to 100 V) JET-MV Low Qg Series
- LFPAK-i Double-Sided Mounting Packages, P-ch. MOS FET Series, and Power-Saving Compact Package Series
- Integrated Power Devices: IC and MOS FET
- Medium-/High-Voltage Power MOS FETs

IGBT

- IGBTs for Industrial and HA Applications
- IGBTs for Strobe Flasher

Triacs and Thyristors



: Any page with this marking is a newly added page.

Power MOS FETs

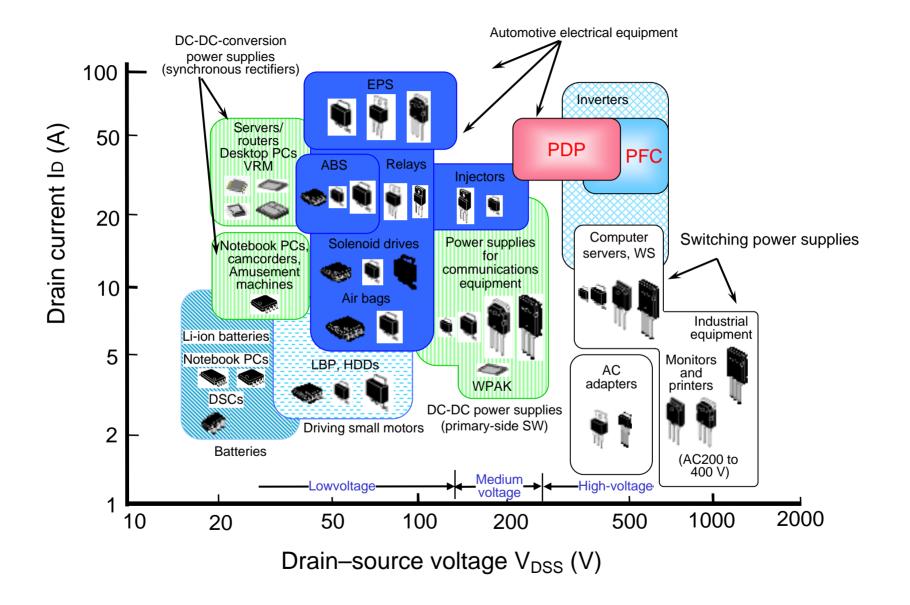
- Applications, Development Trends
- Low-Voltage Power MOS FETs
- 10th Generation Power MOS FETs (V_{DSS}= 30 V)
- New Products: 10th Generation + SBD (Single/Dual)
- Next Generation Products: 11th Generation Power MOS FETs
- New Products: Middle Voltage (40 V to 100 V) JET-MV Low Qg Series
- LFPAK-i Double-Sided Mounting Packages,
 P-ch. MOS FET Series, and Power-Saving Compact Package Series
- Integrated Power Devices: IC and MOS FET
- Medium-/High-Voltage Power MOS FETs



Power MOS FETs

Applications, Development Trends

Power MOS FET and IGBT Application Map



Power MOS FET Trend by Applications

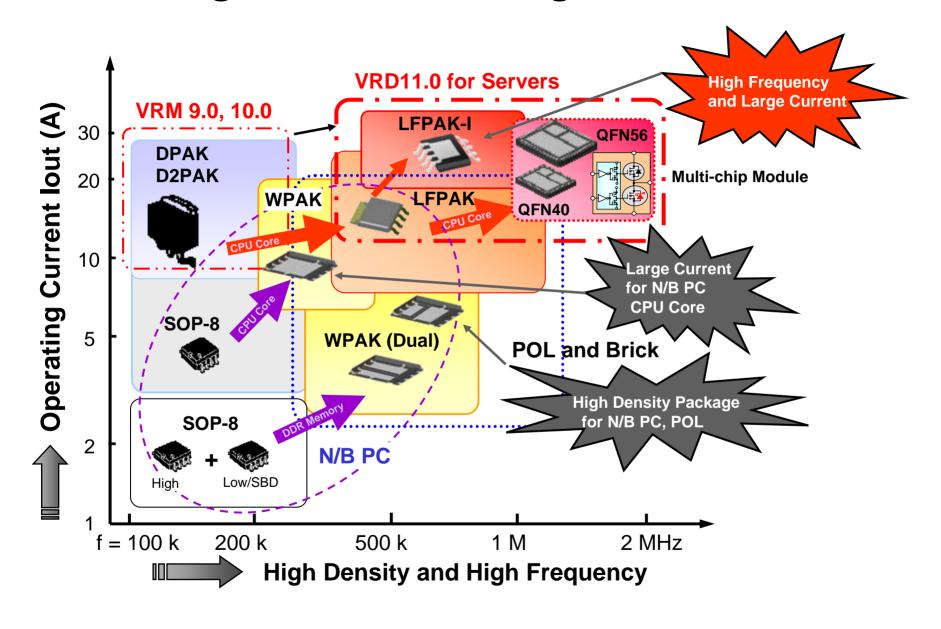
Field	Application	ns	Technical trend	How the power MOS FET suits the task
AV	PDP		 Low power consumption, high brightness Sustained trend for compact modules, bridge method (HIC) 	Medium, high-voltage of 200 to 600 V: Low input capacitance, development of 6th gen. high-voltage series Wafer supply
olies	Network-related devices, AC-DC power supplies		Harmonic regulation supported Power-factor correction (PFC) circuit included Soft-switching method (ZVS) Secondary synchronous rectification	Medium, high-voltage of 250 to 600 V: Low input capacitance, development of 6th gen. high-voltage series Avalanche tolerance guaranteed, built-in high-speed diode (UPS) Ultra-low on-resistance, low Qg, low Qgd, development of 11th gen. low-voltage series Low-voltage of 30 to 100 V
Switching power supplies	Servers, routers, Telecom., communications devices, DC-DC power supplies	Isolated type	2-device/4-device bridge method Active clamp method Secondary synchronous rectification	 Development of 10th gen. power MOS FETs for low/medium voltage of 80 to 100 V, driven by 7 to 10 V. Trench-power MOS FETs for medium voltage of 150 to 250 V, low Ron and low Qdg series. Ultra-low on-resistance, low Qg, low Qgd, development of 10th gen. low-voltage of 30 to 100 V series.
Swit	Distributed power-supply systems Non-isolated type		 Synchronous rectification converter Multi-phase adopted Small and thin POL (point of load) 	 Low-voltage of 12 to 30 V, driven by 2.5 to 10 V Ultra-low on-resistance, low Qg, development of 11th gen. low-voltage series Development of Composite and integration (built-in SBD and driver IC circuit) MOS FET (SOP-8, WPAK, QFN56, QFN40)
Batteries	Mobile phones, Notebook PCs, DSCs		Li-ion battery used Highly functional→ Quick response → Small and thin Increased current capacity	Small, thin, low-resistance, thermal-resistance Package (LFPAK, WPAK) P-ch 8th gen. Ultra-low Ron, two devices in one chip (WPAK) Low-voltage drive: 1.8 to 2.5 V ultra-small and thin Package (CMFPAK-6) Wafer supply Dual-type ultra-small and-thin package (CMFPAK-6)
Motor (PPCs, printers, HDDs) inverters, high-functional robots			Small, low power consumption High precision, quick response Low noise Directly driven by microcomputer	 Medium, high-voltage: 150 to 600 V, DP-8, development of TO-92M series Development of 8th gen. low-voltage SOP-8 (including 2-device packages) series Built-in high-speed diode Development of 6th gen. high-voltage series

Power MOS FETs

Low-Voltage Power MOS FETs V_{DSS} = 12 V to 100 V



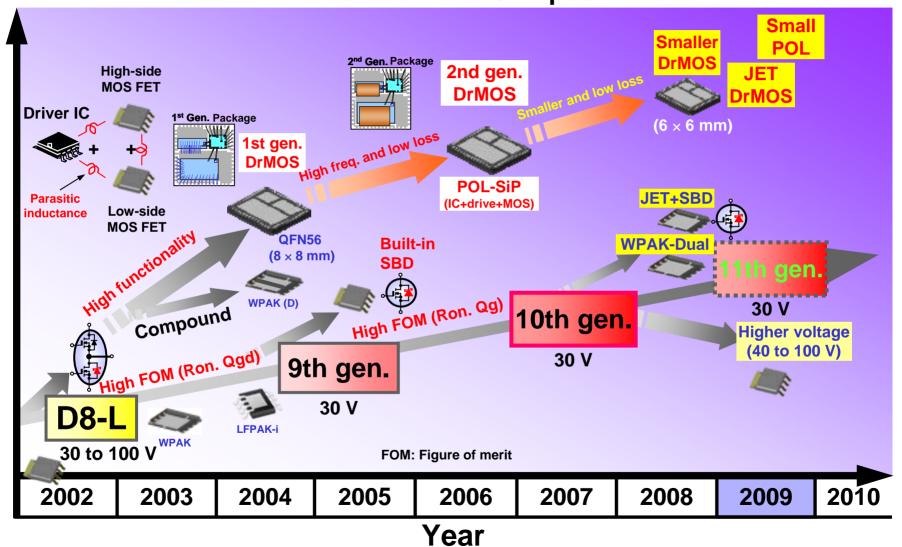
Low-Voltage MOS FET Package Trend



High Frequency and High Efficiency

Roadmap of Power MOS FETs for Highly Efficient Power Supplies

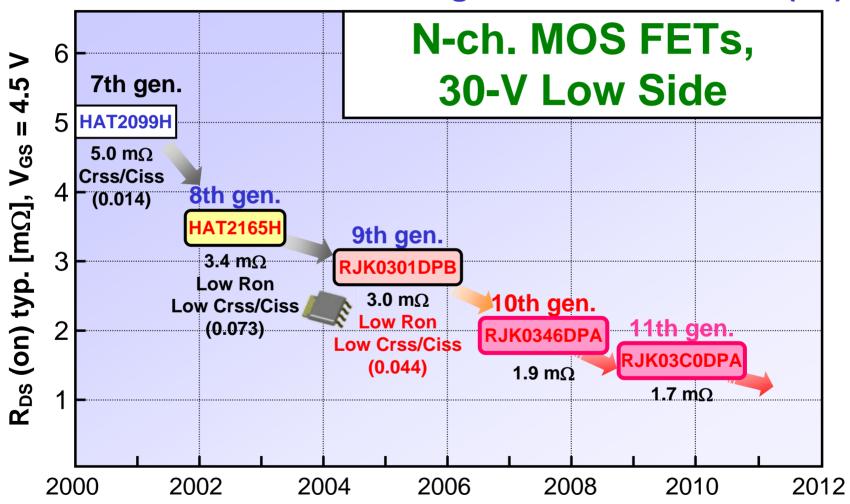
- For Low Loss and More Compact Products -





Roadmap of On-Resistance for Low-Voltage Power MOS FETs

Power MOS FET Technologies and Trend in R_{DS} (on)



Recommended Applications of Low-Voltage MOS FETs for Highly Efficient Power Supplies

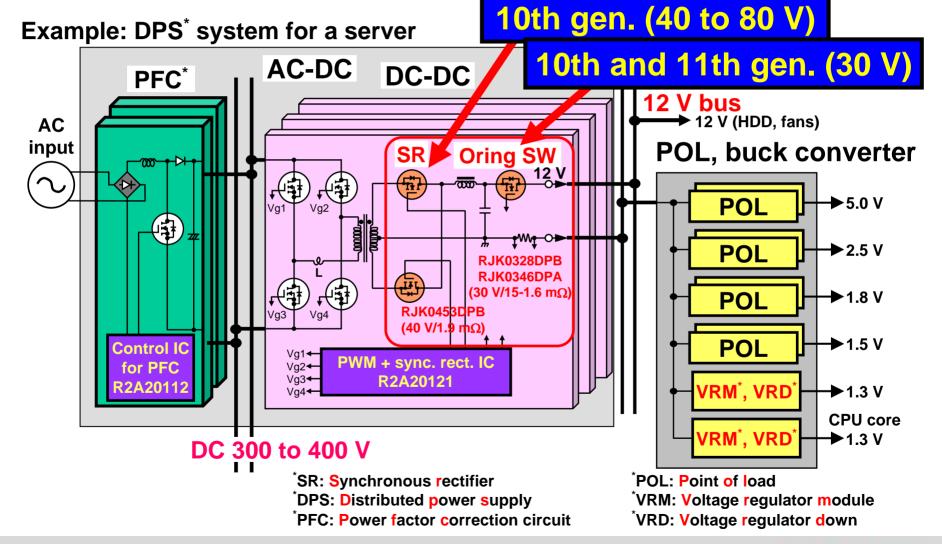
■ DC-DC voltage regulators for driving CPUs, GPUs, memory, etc.

Servers, other network, telecommunications, notebook PCs, VGA

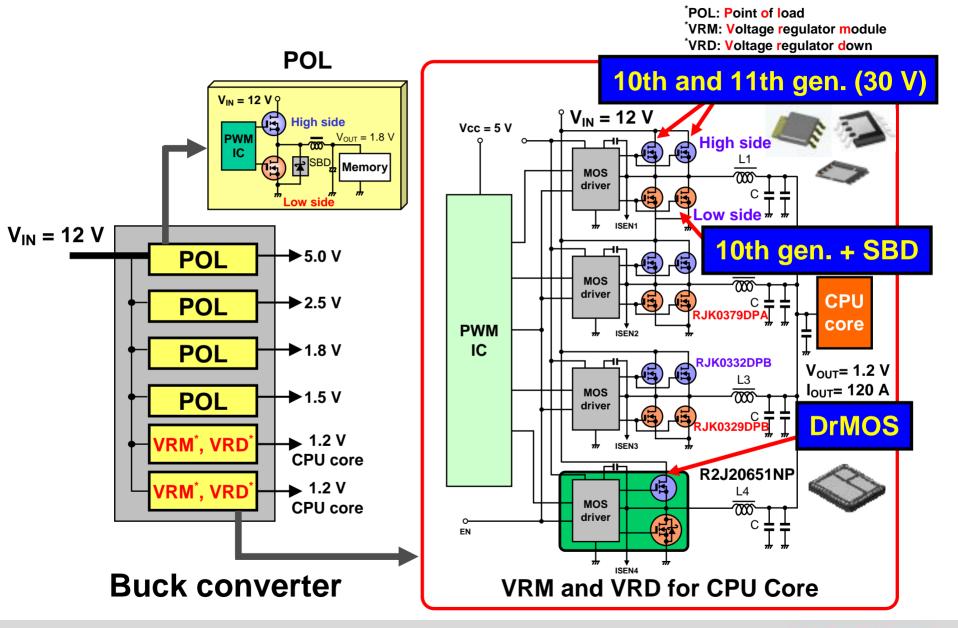


- Isolating bus converters in brick casings (primary and secondary sides) Secondary-side synchronous rectifiers for AC-DC power supplies, ORing switches
 - Servers, routers, telecommunications
- Power management switches (Li-ion battery protection for notebook PCs, etc.)

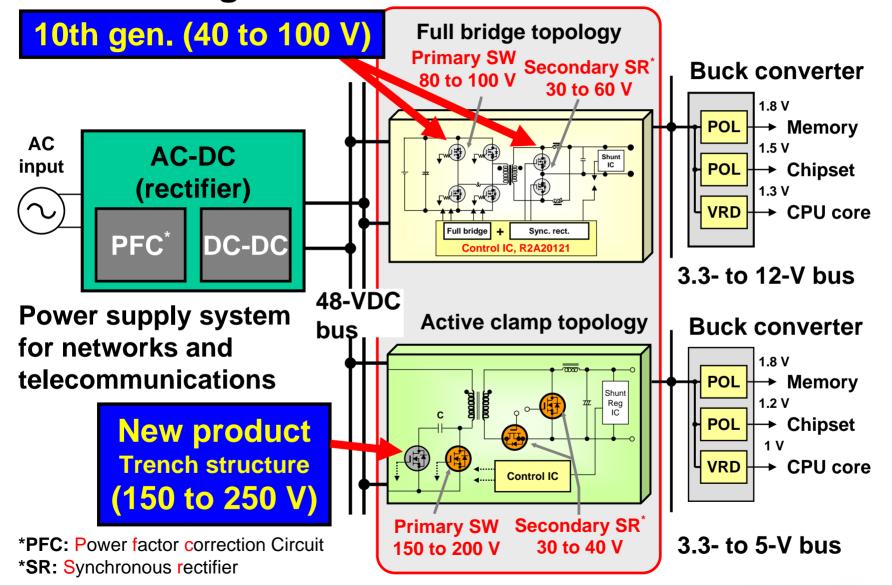
Sample Application: Secondary-Side Synchronous Rectification and ORing Switch for AC-DC **Power Supply**



Sample Application: Power Voltage Regulator

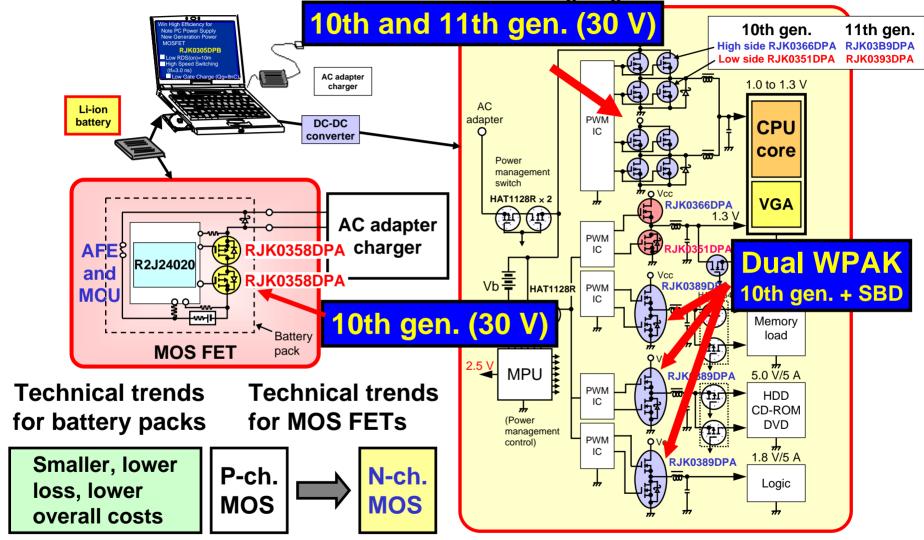


Sample Application: Isolating Bus Converters in Brick Casings



Sample Application: Li-ion Battery for Notebook PC

*VR: Voltage regulator



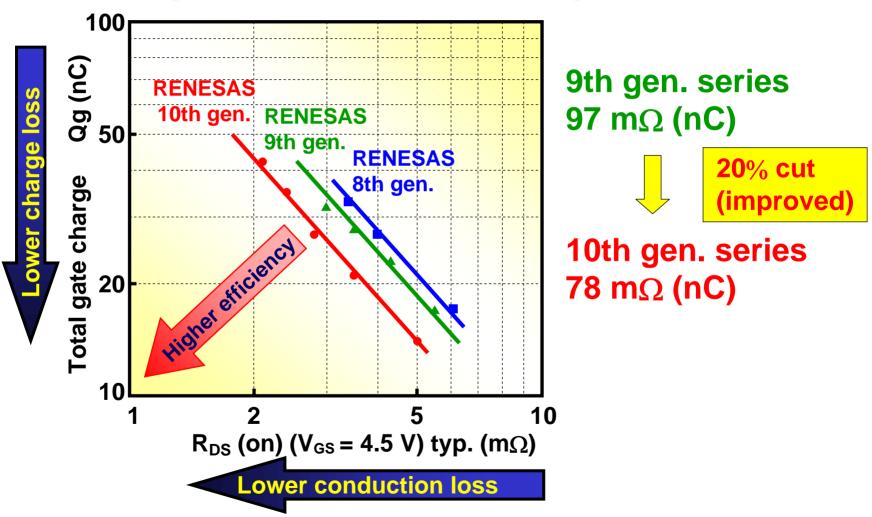
Power section of DC-DC converter

Power MOS FETs

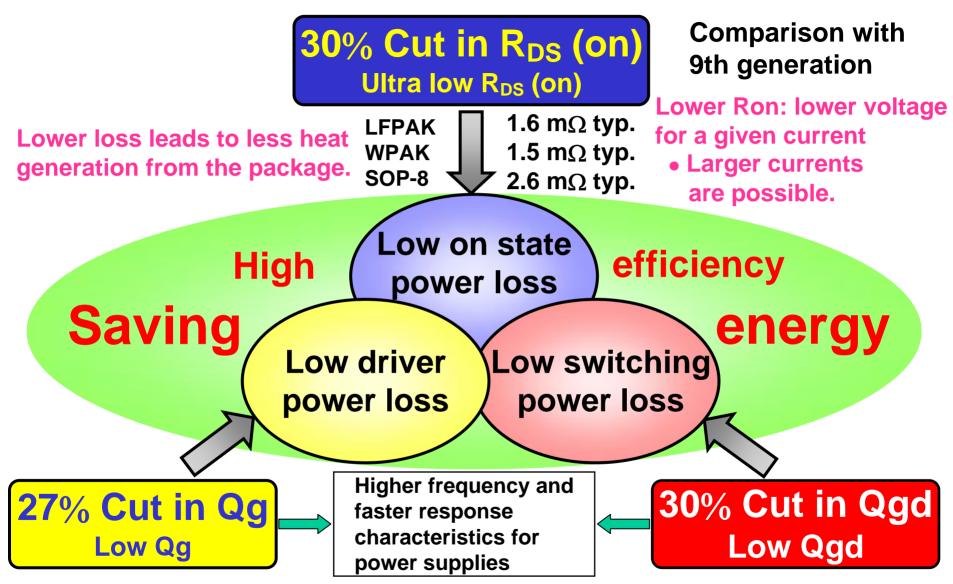
10th Generation Power MOS FETs (V_{DSS}= 30 V)

Performance of 10th Generation Power MOS FETs $(V_{DSS} = 30 \text{ V})$

Figure of merit: FOM (Ron-Qg) at V_{GS} = 4.5 V



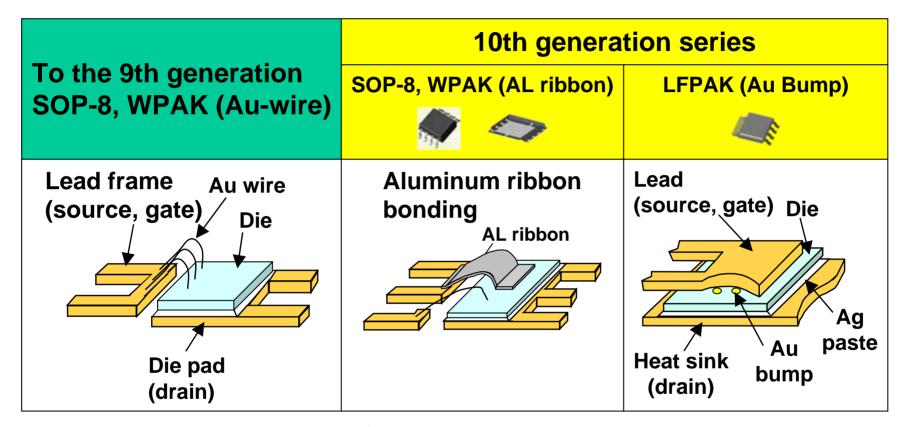
Features of 10th Gen. Power MOS FETs



Making possible smaller and thinner in size



Package Structures for the 10th Generation

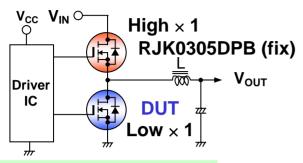


Up to 1.0 m Ω

Up to $0.5 \text{ m}\Omega$

Resistance of package wires is halved (contributing to lower on-resistance).

Data from Efficiency Evaluation of 10th Generation Products

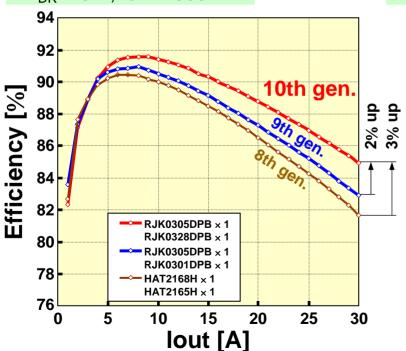


Renesas discrete evaluation board Ta = 25 °C, no air flow $L = 0.45 \mu H$

Test conditions

$$V_{IN} = 12 \text{ V}, V_{OUT} = 1.2 \text{ V}$$

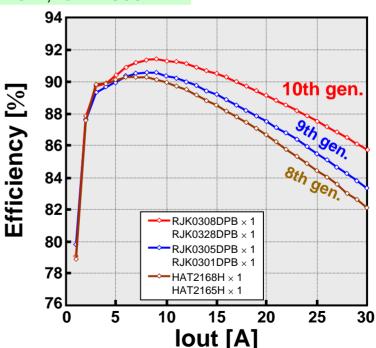
 $V_{DR} = 5 \text{ V}, \text{ fsw} = 500 \text{ kHz}$



Test conditions

$$V_{IN} = 19 \text{ V}, \text{ Vout} = 1.2 \text{ V}$$

 $V_{DR} = 5 \text{ V}, \text{ fsw} = 300 \text{ kHz}$



Lineup of 10th Generation Products in LFPAK Package

for low-side switch and synchronous rectifierfor high-side switch

		Maximum Rating					R _{DS} (or	n) (m Ω	2)	0 21 2	0.5	Schedule	
No.	Part No.	V_{DSS}	V _{GSS}	I_D	P-ch	$V_{GS} = 4.5 \text{ V}$		$V_{GS} = 10 \text{ V}$		Qgd (nC)	Qg (nC)	ES	MP
		(V)	(V)	(A)	(W)	typ.	max.	typ.	max.	(110)	(110)		IVIF
1	RJK0328DPB			60	65	2.1	2.9	1.6	2.1	8.8	42	OK	OK
2	RJK0329DPB		+20/-20 V	55	60	2.4	3.4	1.8	2.3	7.3	35	OK	OK
3	RJK0330DPB	30		45	55	2.8	3.9	2.1	2.7	5.8	27	OK	OK
4	RJK0331DPB			40	50	3.5	4.9	2.6	3.4	4.6	21	OK	OK
5	RJK0332DPB			35	45	5.0	7.0	3.6	4.7	3.0	14	OK	OK

Lineup of 9th Generation Products in LFPAK Package

	Part No.		Maximum R		R _{DS} (or	n) (m Ω	2)	0 1	Qg	Schedule			
No.		V _{DSS}	V _{GSS} (V)	I_D	P-ch	$V_{GS} = 4.5 \text{ V}$		$V_{GS} = 10 \text{ V}$		0 V Qgd (nC)		ES	MP
		(V)		(A)	(W)	typ.	max.	typ.	max.	(1.0)	(nC)		IVIF
1	RJK0301DPB			60	65	3.0	4.0	2.3	2.8	7.0	32	OK	OK
2	RJK0302DPB		+16/-12 V	50	60	3.5	4.6	2.6	3.1	6.0	28	OK	OK
3	RJK0303DPB	30		40	55	4.3	5.6	3.1	3.7	5.2	23	OK	OK
4	RJK0304DPB			35	50	5.5	7.2	4.0	4.8	3.7	17	OK	OK
5	RJK0305DPB			30	45	10.0	13.0	6.7	8.0	1.5	8	OK	OK

Lineup of 10th Generation Products in WPAK Package

for low-side switch and synchronous rectifierfor high-side switch

			Maximum R	ating			R _{DS} (or	n) (mΩ	2)			Sche	edule
No.	Part No.	V_{DSS}	V_{GSS}	I_D	P-ch (W)	$V_{GS} = 4.5 \text{ V}$		$V_{GS} = 10 \text{ V}$		Qgd (nC)	Qg (nC)	ES	MP
		(V)	(V)	(A)		typ.	max.	typ.	max.	(110)	(110)		IVII
1	RJK0346DPA			60	65	1.9	2.7	1.5	2.0	10.5	49	OK	OK
2	RJK0348DPA			50	55	2.5	3.5	1.9	2.5	7.0	34	OK	OK
3	RJK0349DPA			45	50	3.1	4.3	2.4	3.1	5.3	25	OK	OK
4	RJK0351DPA			40	45	4.3	6.0	3.2	4.2	3.7	17	OK	OK
5	RJK0353DPA	30	+20/-20 V	35	40	5.4	7.6	4.0	5.2	3.0	14	OK	OK
6	RJK0355DPA	30	+20/-20 V	30	25	11.8	16.5	8.2	10.7	1.4	6.3	OK	OK
7	RJK0364DPA			35	35	8.0	11.2	6.0	7.8	2.2	10	OK	OK
8	RJK0365DPA			30	30	9.6	13.4	7.0	9.1	1.7	7.6	OK	OK
9	RJK0366DPA			25	30	12.0	16.8	8.5	11.1	1.5	6.8	OK	OK
10	RJK0368DPA			20	25	16.0	22.4	11.0	14.3	1.3	6.2	OK	OK

Lineup of 10th Generation Products in SOP-8 Package

for low-side switch and synchronous rectifierfor high-side switch

			Maximum R	ating			R _{DS} (or	n) (mΩ	2)			Sche	edule
No.	Part No.	V _{DSS}	V_{GSS}	I_D	P-ch (W)	$V_{GS} = 4.5 \text{ V}$		$V_{GS} = 10 \text{ V}$		Qgd (nC)	Qg (nC)	ES	MP
		(V)	(V)	(A)		typ.	max.	typ.	max.	(110)	(110)	LO	IVII
1	RJK0348DSP			22	2.5	3.2	4.5	2.6	3.4	7.0	34	OK	OK
2	RJK0349DSP			20	2.5	3.6	5.0	2.9	3.8	5.3	25	OK	OK
3	RJK0351DSP			20	2.5	5.0	6.9	4.0	5.2	3.7	17	OK	OK
4	RJK0352DSP		+20/-20 V	18	2.0	5.5	7.0	4.3	5.6	3.4	16	OK	OK
5	RJK0353DSP	30		18	2.0	5.9	8.3	4.5	5.9	3.0	15	OK	OK
6	RJK0354DSP	30		16	2.0	7.5	10.5	5.4	7.0	2.5	12	OK	OK
7	RJK0355DSP			12	1.8	12.0	16.8	8.5	11.1	1.4	6.0	OK	OK
8	RJK0366DSP			11	2.0	12.5	17.5	9.0	11.7	1.5	6.5	OK	OK
9	RJK0369DSP			9	1.8	16.0	22.5	12.0	15.6	1.2	5.6	ОК	OK
10	RJK0371DSP			8	1.8	19.0	27.0	14.0	19.0	1.0	3.8	OK	OK



Power MOS FETs

New Products: 10th Generation + SBD (Single/Dual)

SBD: Shottky barrier diode



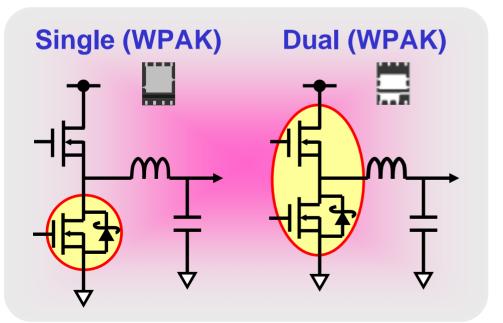
10th Generation MOS FET Plus On-Chip SBD

(Single/Dual)



Main Applications

- Servers/PCs (CPU/memory)
- Graphics cards (VGA/MXM)
- Telecomms (secondary-side synchronous rectification)



SBD: Schottky barrier diode

WPAK

Features (Single)

- On-chip SBD between source and drain
 - Achieve higher power efficiency Lower V_{DF} loss during dead time
 - Reduced EMI noise: Lower spike voltage between low-side D and S when high-side switch is turned on

Features (Dual)

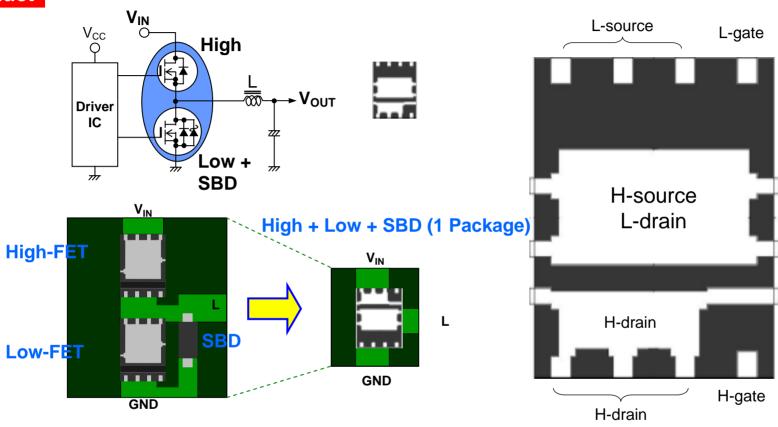
- Inclusion of 2 switching devices for high and low sides in one package
 - Reduces PCB footprint by 50%, enabling more compact designs
- On-chip SBD for low-side switching device
 - Achieve higher power efficiency Lower V_{DF} loss during dead time
 - Reduced EMI noise: Lower spike voltage between low-side D and S when high-side switch is turned on

Reduction of Spike Voltages (Comparison of Operating Frequency)

 $V_{IN} = 12 \text{ V}, V_{OUT} = 1.2 \text{ V},$ $V_{DR} = 5 V$, fsw = 300 kHz, The waveforms in are those when the High side: $L = 0.45 \mu H, I_{OUT} = 25 A$ high-side switching device turned on. RJK0365DPA Low side: RJK0381DPA Low: RJK0351DPA **V**_G (H) (on-chip SBD) (without SBD) V_G(H) V_{GS} (L) $V_{DS}(L)$ 80 ns/div 80 ns/div Reduction in low-side Vp = 27.2 Vspike voltage Vp = 22.4V_{DS} (L) energy and **-17%** V_G (H) **Reduced EMI noise** V_{GS} (L) 4 ns/div 4 ns/div

New Product: 10th Generation in WPAK (Dual)





Reduction of PCB mounting area; more compact

Back of the package

Lineup of 10th Generation Power MOS FET Plus On-Chip SBD Products



WPAK Single



	Part No.		Max. ratin	igs			R _{DS} (or	n) (m Ω)			Schedule	
No		V_{DSS}	V _{GSS} (V)	I _D	Pch	$V_{GS} = 4.5 \text{ V}$		V _{GS} = 10 V		Qgd (nC)	Qg (nC)	ES	MP
		(V)		(A)	(W)	typ.	max.	typ.	max.	(***)	(***)		IVIF
1	RJK0379DPA		+20/-20	50	55	2.4	3.4	1.8	2.3	10.7	37	ОК	ОК
2	RJK0380DPA	30 V		45	50	3.3	4.7	2.4	3.2	6.7	24	ОК	ОК
3	RJK03A4DPA	30 V		42	45	4.3	6.0	2.9	3.8	5.2	17	ОК	ОК
4	RJK0381DPA			40	45	4.7	6.6	3.4	4.5	4.3	15	OK	ОК

WPAK Dual

No	Part No.	FET			R _{DS} (on) (m Ω))	.		Sche	edule			
			V _{DSS} (V)	V _{GSS} (V)	I _D	Pch	V_{GS} = 4.5 V		V _{GS} = 10 V		Qgd (nC)	Qg (nC)	ES	MP
					(A)	(W)	typ.	max.	typ.	max.	()	()	LS	IVIE
1	RJK0389DPA	High	30	+20/-20	15	10	11.8	16.5	8.2	10.7	1.4	6	ОК	ОК
'		Low	30	+20/-20	20	10	10.5	14.7	6.8	8.9	2.2	7.2		

Attention: This product is under development. The electrical characteristics or schedule may be subject to change without notice.

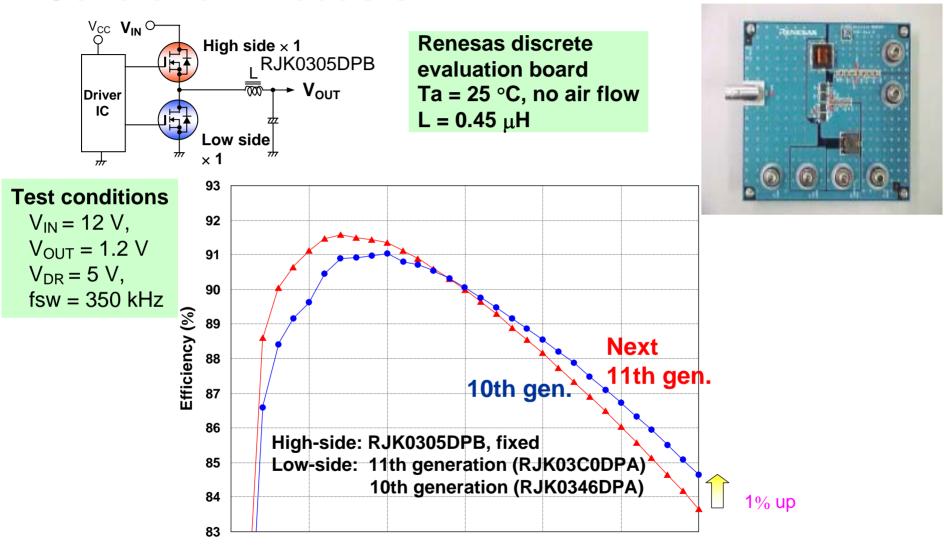


Power MOS FETs

Next Generation Products: 11th Generation Power MOS FETs



Data From Efficiency Evaluation of 11th Generation Products



20

25

30

15

lout (A)

10

0

5

Development Schedule for Next (11th) Generation Products

Package: WPAK

for low-side switch and synchronous rectification for high-side switch

			Max. rati	ngs			R _{DS} (on) (m Ω)	Oad	_	_	Sc	hedule	Current																												
No	Part No.	V_{DSS}	V _{GSS}	I _D	Pch	V _{GS} =	4.5 V	$V_{GS} = 10 \text{ V}$		Qgd (nC)	Qg (nC)	Rg	ES	MP	Products																												
		(V)	(V)	(A)	(W)	typ.	max.	typ.	max.	(***)	` ,		LS	IVIE	(JET Series)																												
1	RJK03C0DPA			70	65	1.8	2.5	1.5	2.0	13.7	66	0.75	OK	OK	-																												
2	RJK0390DPA							65	60	2.1	2.9	1.7	2.2	11.3	54	0.8	ОК	OK	RJK0346DPA																								
3	RJK0391DPA			50	50	2.8	3.9	2.2	2.9	7.4	34	0.95	OK	OK	RJK0348DPA																												
4	RJK0392DPA								45	45	3.4	4.8	2.7	3.5	5.9	26	0.8	ОК	OK	RJK0349DPA																							
5	RJK0393DPA				40	40	4.2	5.9	3.3	4.3	4.7	21	1.4	OK	OK	RJK0351DPA																											
6	RJK0394DPA			35	35	5.3	7.4	4.1	5.3	3.7	15.5	1.4	OK	OK	RJK0353DPA																												
7	RJK0395DPA	30	+20 /-20 V	30	30	7.6	10.6	5.9	7.7	2.6	11.0	2.2	OK	OK	RJK0364DPA																												
8	RJK0396DPA		, == -																				30	28	9.0	12.6	6.9	9.0	2.2	9	2.5	OK	OK	RJK0365DPA									
9	RJK0397DPA																																			30	25	10.4	14.6	7.8	10.1	1.9	7.4
10	RJK03B7DPA																																30	30	7.7	10.7	6.0	7.8	2.6	11.0	1.0	OK	OK
11	RJK03B8DPA			30	28	9.3	12.9	7.0	9.3	2.2	9	1.2	OK	OK	RJK0365DPA																												
12	RJK03B9DPA			30	25	10.9	15.1	8.3	10.6	1.9	7.4	1.2	ОК	OK	RJK0355, 66DPA RJK0368DPA																												

Attention: This product is under development. The electrical characteristics or schedule may be subject to change without notice.







Power MOS FETs

New Products: Middle Voltage (40 V to 100 V) JET-MV Low Qg Series

JET Middle Voltage Series





Target Application

- Server (D2D)
- Telecom (Brick)
- Isolated DC/DC converter

Feature

Lineup

Low Qg series: Low SW loss.

Various V_{DSS} series

V_{DSS}: 40 V, 60 V, 80 V, 100 V

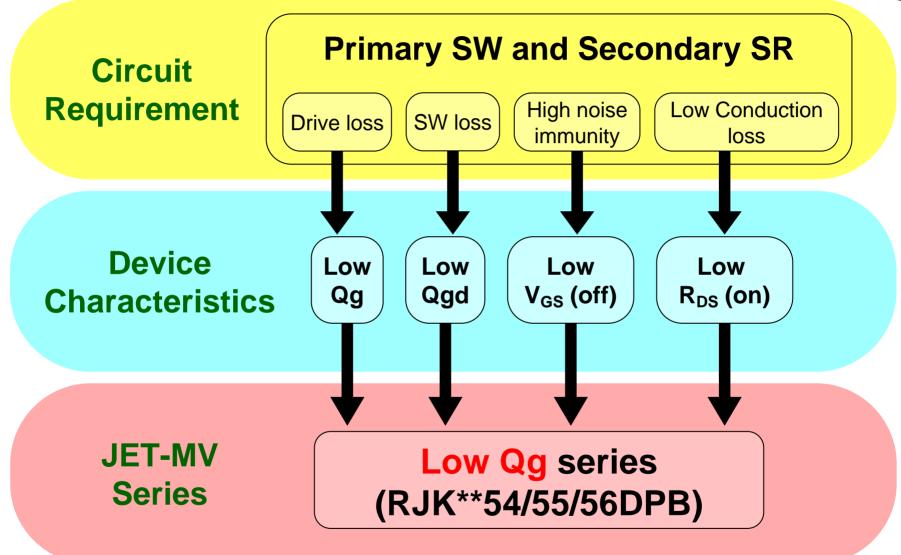
Improving FOM

Ron • Qdg, Ron • Qg

Isolated DC/DC Converter **Primary: Secondary:** for Switching for Synchronous Rectifier Full Bridge Synchronous Rectification + Control MOSFET Control

Recommended JET Middle Voltage Series



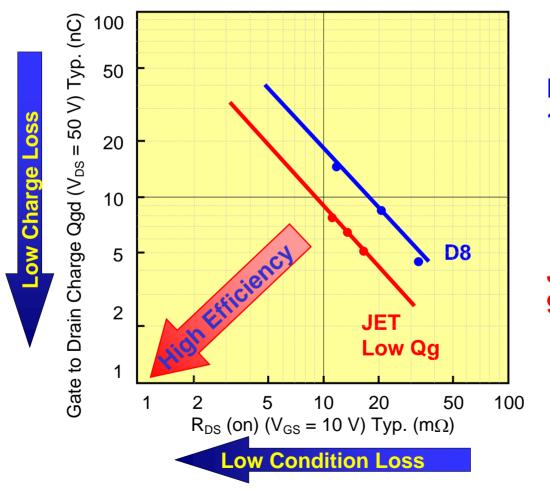


Low Gate Charge (Qg) JET Middle Voltage. $(V_{DSS} = 100 \text{ V})$



For Primary SW

Figure of Merit: FOM (Ron • Qdg) at V_{DS} = 50 V



D8 180 mΩnC



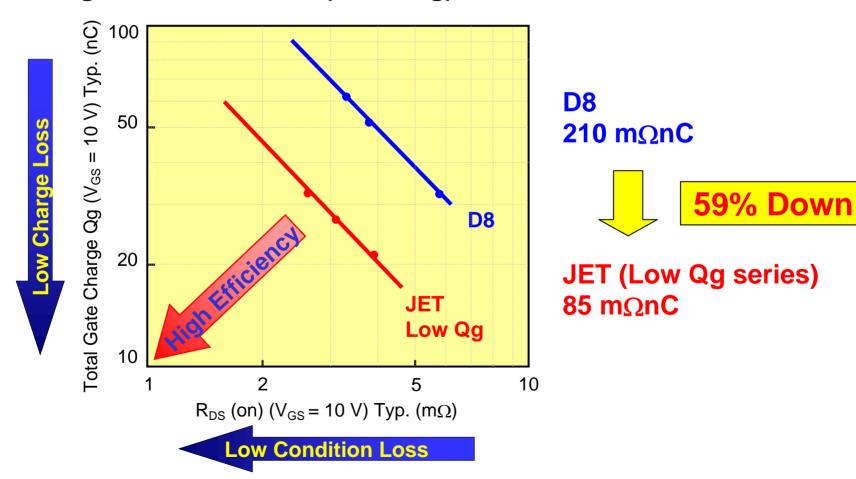
JET (Low Qg series) 90 mΩnC

Low Gate Charge (Qg) JET Middle Voltage. $(V_{DSS} = 40 \text{ V})$



For Secondly SR

Figure of Merit: FOM (Ron • Qg) at V_{GS} = 10 V



MOS FET Recommendation for Next Bricks

Application	Pout (W)	Topology	V _{DSS} (V)	Primary SW	V _{DSS} (V)	Secondary SR
Bus Converter	120 to 240	Half Bridge Full Bridge	100	RJK1056DPB × 2 RJK1055DPB × 4	60 80	RJK0654DPB × 2 RJK0854DPB × 2
V _{IN} = 36 to 75 V V _{OUT} = 12 V	300 to 700	Full Bridge	100	RJK1056DPB × 4 RJK1056DPB × 8	60 80	RJK0656DPB × 4 RJK0856DPB × 4
Isolated Converter V _{IN} = 38 to 55 V	30 to 90	Forward Active Clamp	150	RJK1557DPA × 1	40	RJK0454DPB × 2
V _{OUT} = 3.3 V, 5.5 V	100 to 200	Half Bridge	80	RJK0856DPB × 2	40	RJK0455DPB × 2 RJK0456DPB × 4
PA Converter	300 to	Full Bridge	100	RJK1056DPB × 4	100	RJK1055DPB × 4
V _{IN} = 36 to 75 V V _{OUT} = 28 V	500	1 dii Diidge	100	RJK1056DPB × 8	100	RJK1056DPB × 4

Frequency: Forward Active Clamp f = 300 to 500 kHz, Half Bridge f = 250 to 400 kHz, Full Bridge f =150 to 200 kHz Drive Voltage: Primary $V_{GS} = 7$ to 10 V, Secondary $V_{GS} = 7$ to 8 V



Low Qg JET Middle Voltage Series Lineup



Main application : DC/DC Power Supply and Motor Drive,
 Battery Power Management etc.

- Feature : Low Qg and Qdg (Low Switching loss)

High Threshold Voltage (High noise immunity)



		Max. rat	ings		V _{GS} (off)	R _{DS} (o	n) (m Ω)	Qdg	Qg	Sche	edule
Type No.	V_{DSS}	V_{GSS}	I _D	Pch	[V]	V _{GS} =	= 10 V	(nC)	(nC)	OCITE	
	(V)	(V)	(A)	(W)	min-max	typ.	max.	V _{GS} =	10 V	ES	MP
RJK0454DPB			40	55	2.0-4.0	3.9	4.9	3.2	22	OK	OK
RJK0455DPB	40		45	60	2.0-4.0	3.1	3.8	4.1	27	OK	OK
RJK0456DPB			50	65	2.0-4.0	2.6	3.2	4.9	33	OK	OK
RJK0654DPB			30	55	2.0-4.0	6.5	8.3	3.3	22	OK	OK
RJK0655DPB	60		35	60	2.0-4.0	5.3	6.7	4.2	28	OK	OK
RJK0656DPB		.00	40	65	2.0-4.0	4.5	5.6	5.0	34	OK	OK
RJK0854DPB		±20	25	55	2.0-4.0	10	13	5.0	30	OK	OK
RJK0855DPB	80		30	60	2.0-4.0	8.2	11	6.3	37	OK	OK
RJK0856DPB			35	65	2.0-4.0	6.9	8.9	7.6	45	OK	OK
RJK1054DPB			20	55	2.0-4.0	17	22	5.1	30	OK	OK
RJK1055DPB	100		23	60	2.0-4.0	13	17	6.5	38	OK	OK
RJK1056DPB			25	65	2.0-4.0	11	14	7.8	45	OK	OK

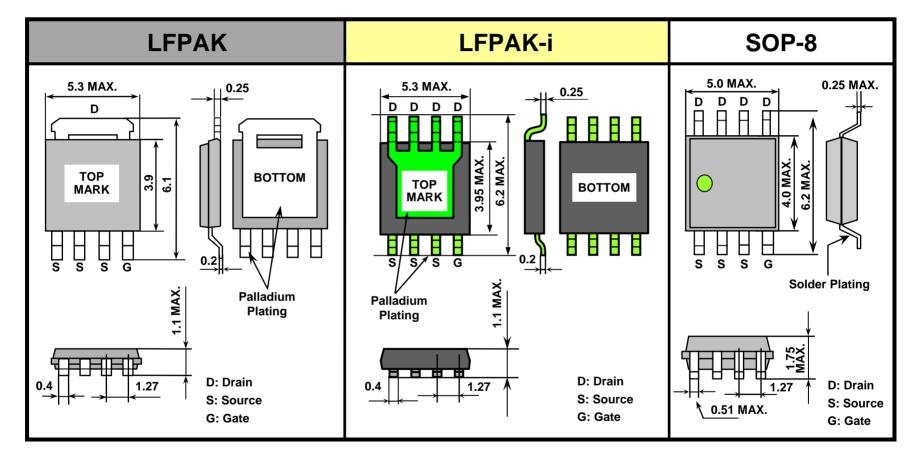
Note) The development plan and the characteristics of this series may be changed without notice.



Power MOS FETs

LFPAK-i Double-Sided Mounting Packages, P-ch. MOS FET Series, and Power-Saving Compact Package Series

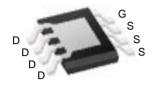
LFPAK and LFPAK-i (SOP-8) Comparison of Package Dimensions



UNIT: mm

LFPAK-i Package Power MOS FET Series



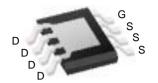


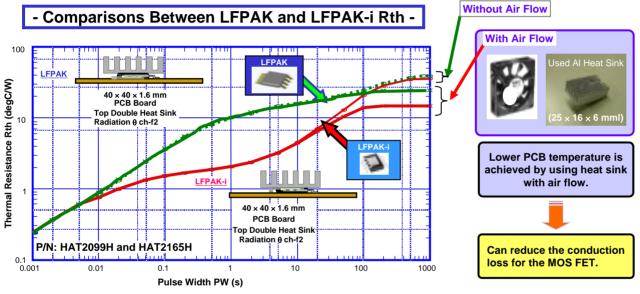
- Features -

- 40% of mounting thermal resistance is reduced and 30% of current improvement is realized
- SOP-8 and LFPAK of substitutions
- Top side cooling capability

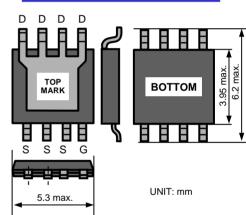
- Application -

- Server of VR (Voltage Regulator)
- VR of High-side to HAT2168N
 Low-side to HAT2165N/HAT2166N





- Package Dimension -

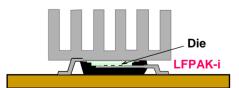


- Lineup -

	*[]: V _{GS} = 8 V													
	Rat	ings		R _{DS} (or	n) (mΩ)		Qg	Qgd	Sch	edule				
Part No.	V _{DSS}	I _D	V _{GS} =	4.5 V*	V _{GS} =	= 10 V	typ.	typ.	WS	MP				
	(V)	(A)	typ.	max.	typ.	max.	(nC)	(nC)	VVS	IVIP				
HAT2165N	30	55	3.7	5.6	2.8	3.6	33	7.1	OK	OK				
HAT2166N	30	45	4.3	6.4	3.2	4.1	27	5.9	OK	OK				
HAT2168N	30	30	9.1	13.8	6.3	8.2	11	2.4	OK	OK				
HAT2172N	40	30	(6.9)	(9.5)	6.1	7.8	32	4	OK	OK				
HAT2173N	100	25	[13.3]	[17.8]	12.3	15.3	61	14.5	OK	OK				
HAT2174N	100	20	[22]	[30]	21	27	33.5	8.4	OK	OK				
HAT2175N	100	15	[34]	[46]	33	42	21	4.5	OK	OK				

Top Side Cooling Capability

Heat Sink



PCB Board

P-channel MOS FET Series

Feature : Super-Low R_{DS} (on) HAT1125H R_{DS} (on) = 2.7 $m\Omega$

Application: Li-ion Battery Protect Circuit

Load SW, Charger for Note-Book PC

				V _{GSS}	_	4.5 V R	_{DS} (on)	10 V R	DS (on)			Sch	edule
No.	Part No.	Package	V _{DSS} (V)	V _{GSS} (V)	Ι _D (A)	typ.	max.	typ.	max.	Qg (nC)	Qgd (nC)	WS	MP
			(-)	(-)	(* -)	$(m\Omega)$	$(m\Omega)$	$(m\Omega)$	$(m\Omega)$	(IIC)	(IIC)	***	1711
1	HAT1125H	LFPAK			-45	4.1	5.9	2.7	3.6	165	40	OK	OK
2	HAT1127H	\(\)			-40	6.0	8.6	3.6	4.5	125	28	OK	OK
3	RJK0315DSP	SOP-8			-16	7.2	10.5	5.2	6.5	48	20	ОК	OK
4	RJK0318DSP	TE TU	-30	+10/-20	-12	14.0	22.0	9.5	12.0	22	10	ОК	OK
5	RJK0319DSP				-10	19.0	28.0	12.5	15.5	17	5.5	ОК	OK
6	RJK0315DPA	WPAK			-35	6.8	10.0	4.8	5.9	48	20	OK	'10/2

Next Generation Compact Low-Loss Power MOS FET CMFPAK-6 Series





Renesas power MOS FET series in a small package can realize smaller and lighter mobile devices

Power MOS FET incorporated in CMFPAK-6

- Gate driving voltage: 1.8 to 2.5 V
- P-ch/N-ch products using D8 process
- Suitable for step-up/down DC-DC converters for mobile devices (small set) and power management

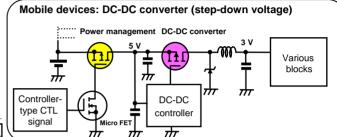
Main applications

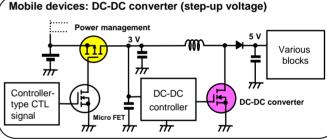
- Digital still cameras
- Mobile phones
- PDAs, etc.

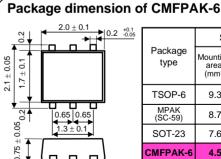
Product Lineup

Note 1: Numbers in R_{DS} (on) are indicated as typ./max. Note 2: Please contact our sales department for delivery date.

			Max	imum Ratir	ngs		Electrical	Characteris	stics			Sch	nedule	П
Polarity	Part No.	Drive Voltage (V)	V _{DSS} (V)	V _{GSS} (V)	I _D (A)	R _{DS} (on) (mΩ) at 10 V	$R_{DS}(on)$ (m Ω) at 4.5 V	$R_{DS}(on)$ $(m\Omega)$ at 2.5 V	$R_{DS}(on)$ $(m\Omega)$ at 1.8 V	Ciss (pF)	Marking	SPL	MP	/
	HAT1069C				-4.0	_	38/52	48/70	60/93	1380	VY-			П
	HAT1093C				-3.0		41/54	54/76	85/128	940	VM-			П
	HAT1094C	1.8	-12	±8	-2.5		67/88	90/126	128/192	530	VN-	OK	OK	П
	HAT1095C				-2.0		108/140	146/205	225/337	290	VP-			П
NE	RJJ0102DQM				-1.2		265/315	400/535	625/930	123	TBD			П
	HAT1090C				-2.5		50/65	74/104		590	VJ-			П
Р	HAT1089C	2.5	-20	±12	-2.0	<u> </u>	79/103	120/168		365	VK-	ОК	ок	П
	HAT1091C	2.5	_20		_1.5	<u> </u>	134/175	205/287		200	VL-		Oit	П
	HAT1096C				-1.0	_	225/293	380/530	_	155	VQ-			١١
	HAT1108C		_30		_1.5	155/194	245/356			160	VZ-			ı
NE	WHAT1142C	4.5		+20/–10	-3.0	50/63	75/109			505	TBD	ок	ок	1
	HAT1111C	4.5	-60	+20/-10	-2.0	245/307	310/450			290	UA-		OK	П
	HAT1141C		-80		-0.8	800/1050	1020/1380	_	_	170	UM-			П
	HAT2204C				3.5	<u> </u>	26/34	34/44	45/69	770	VU-			П
	HAT2205C	1.8	12	±8	3		38/50	48/67	65/97	430	VV-	OK	OK	П
	HAT2206C				2	_	65/85	81/114	113/170	260	VW-			П
	HAT2202C				3	<u> </u>	31/40	43/55		520	VR-			П
	HAT2196C	2.5	20	±12	2.5	<u> </u>	45/58	66/93	<u> </u>	270	VS-	ОК	ок	П
	HAT2203C	2.0	20	· -	2		69/90	107/150		165	VT-	Oit	Oit	П
N	HAT2207C				1.5		100/130	140/210	_	135	VX-			П
NE	WRJK0320DQM	2.5	30	±12	4.0	_	30/39	40/58	_	510	TBD	OK	OK	П
	HAT2268C	4.5	30	+20/-10	4.0	27/34	37/54	<u> </u>	<u> </u>	440	UN-	ок	ок	П
	HAT2221C	4.5	- 50	+20/-10	1.5	120/150	160/235	_	_	110	UC-	OIX	OIX	١١
	HAT2240C				2.5	<u> </u>	75/98	85/119		590	UK-			1
	HAT2281C	2.5	60	±12	2.0		120/156	140/196		350	UH-	OK	OK	
	HAT2282C				1.5		195/254	240/336	_	210	UJ-			
	HAT2217C	4.5		+20/-10	3.0	105/132	126/183	_	_	275	UB-	OK	OK	







	Size	Э	Heig	ht
Package type	Mounting area (mm²)	Ratio	Package (mm)	Ratio
TSOP-6	9.3	1.00	1.10	1.00
MPAK (SC-59)	8.7	0.94	1.35	1.23
SOT-23	7.6	0.82	1.12	1.02
CMFPAK-6	4.5	0.49	0.80	0.73

CMFPAK-6 Dual Type Power MOS FET



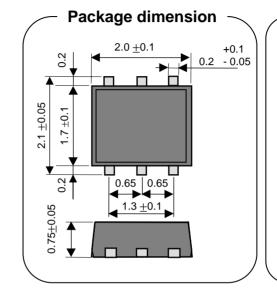
Features

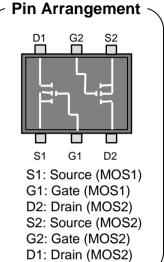
- Dual (N-ch Dual, P-ch Dual, N-ch + P-ch)
- Low-voltage drive (1.8 V, 2.5 V)
- Small package (CMFPAK-6)
- High speed switching

Applications

- DC-DC converter
- Motor drive
- Power Management switch

Lineup





		Drive	Maxi	mum Rat	ings		Electrical chara	cteristics		Sche	dulo
Polarity	Part No	voltage	V_{DSS}	V_{GSS}	I _D	R _{DS}	(on) (m Ω) (typ./r	max.)	Ciss	Scrie	aule
		(V)	(V)	(V)	(A)	$V_{GS} = 4.5 \text{ V}$	$V_{GS} = 2.5 \text{ V}$	$V_{GS} = 1.8 \text{ V}$	(pF)	SPL	MP
P-ch	HAT1146C	1.8	-12	±8	-1.2	265/330	400/565	625/1130	125	ОК	OK
(Dual)	HAT1147C	2.5	-20	±12	-1.0	340/440	575/960	-	85	UK	
NI ali	HAT2291C	1.8	12	±8	1.8	150/200	200/290	265/440	100		
N-ch (Dual)	HAT2292C	2.5	20	140	1.5	165/215	255/370	-	73	ОК	OK
(Duai)	HAT2286C	2.5	60	±12	0.9	460/595	560/770	-	80		
	HAT3042C	1.0	12	. 0	1.8	150/200	200/290	265/440	100		
N ab i D ab	ПА I 3042C	1.8	-12	±8	-1.2	265/330	400/565	625/1130	125		OK
N-ch + P-ch	LIAT2042C	2.5	20	140	1.5	165/215	255/370	-	73	OK	OK
HAT3043C	HA 13043C	2.5	-20	±12	-1.0	340/440	575/960	-	85		

Power MOS FETs

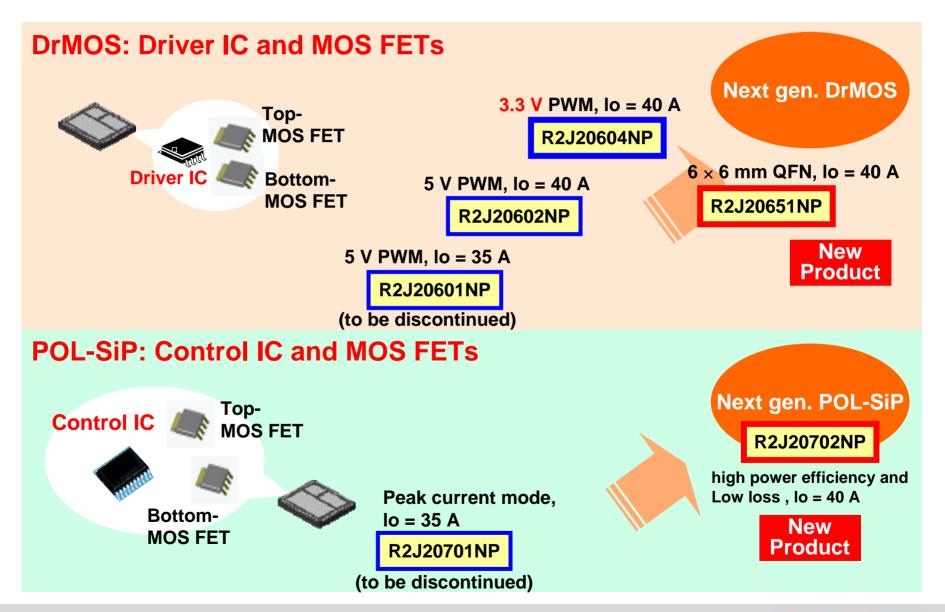
Integrated Power Devices: IC and MOS FET

Driver IC and MOS FET integrated in SiP: DrMOS

PWM controller and MOS FET integrated in SiP: POL-SiP



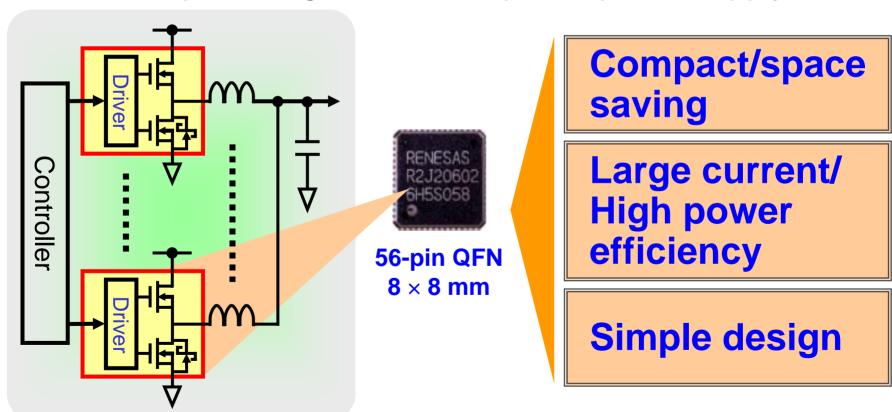
Product Family: IC and MOS FET Integrated in SiP



DrMOS (R2J20602NP) (1)

Driver IC, MOS FET × 2 → Incorporated in a single package

Sample configuration: Multiphase power supply



DrMOS (R2J20602NP) (2)

Compact package: QFN saves space.

Configuration of discrete device

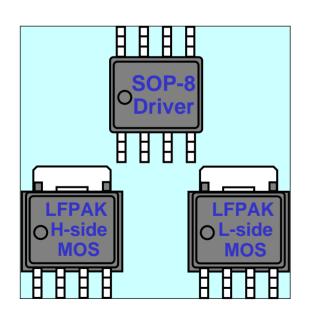
Configuration of DrMOS

Mounting area

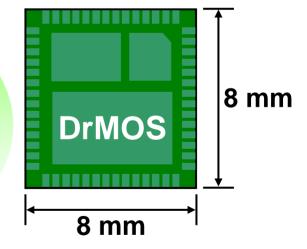
 $= 150 \text{ mm}^2$



 $= 64 \text{ mm}^2$



43% cut
In mounting area

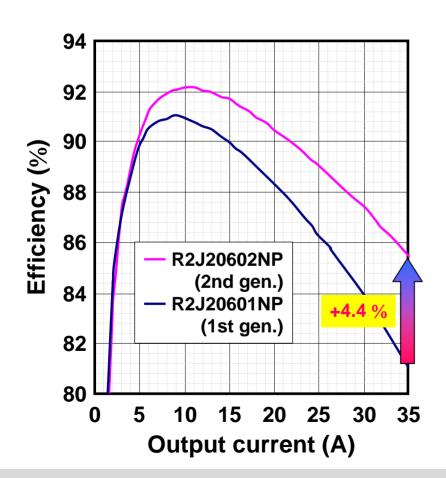


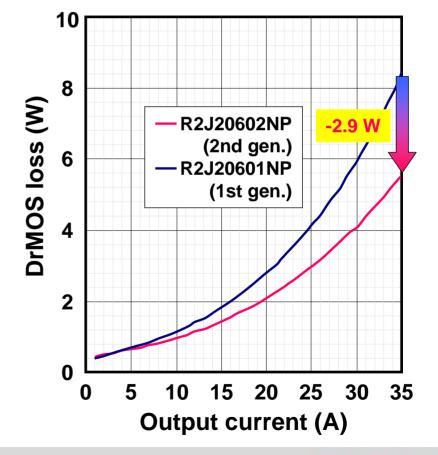
DrMOS (R2J20602NP) (3)

Package with wireless structure contributes to better performance.

Test conditions

 $V_{IN} = 12 \text{ V},$ $V_{OUT} = 1.3 \text{ V},$ fsw = 600 kHz,No Airflow





DrMOS (R2J20604NP)



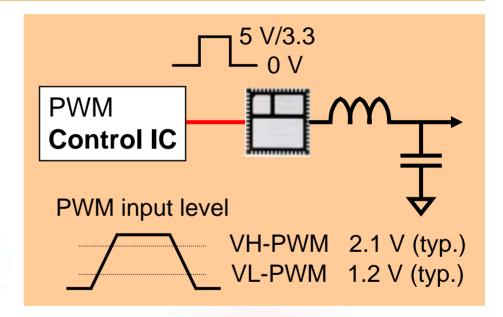
3.3-V PWM input covers a wealth of applications.

Available in combination with various control ICs.

Digital 3.3 V PWM controller

Analog 5.0 V PWM controller

Analog 3.3 V
PWM controller





DrMOS (R2J20651NP) (1)

40-pin QFN (6×6) saves more space.

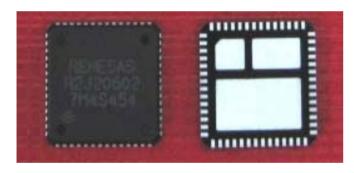
R2J20602NP

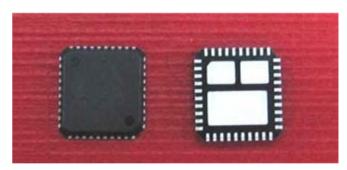


Configuration of DrMOS

Mounting area = 64 mm^2







56-pin QFN (8 × 8 mm)

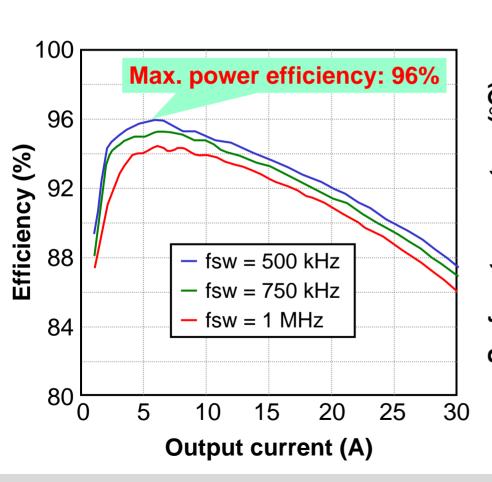
44% cut in mounting area

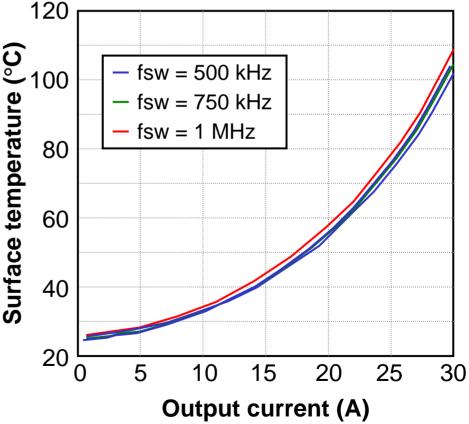
40-pin QFN (6 × 6 mm)

DrMOS (R2J20651NP) (2)

Low loss and high power efficiency keeps heat generation down.

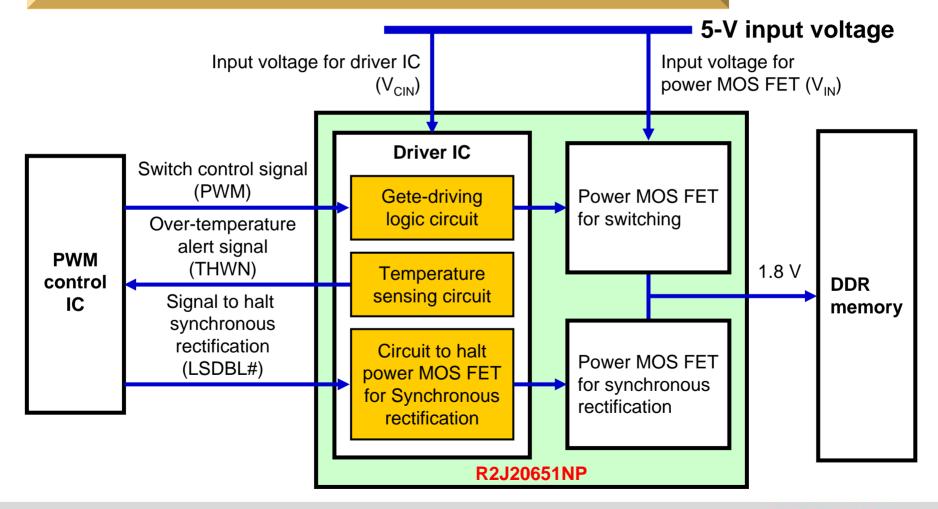
Test conditions $V_{IN} = 5 \text{ V},$ $V_{OUT} = 1.8 \text{ V},$ no air flow,
no heat sink





DrMOS (R2J20651NP) (3)

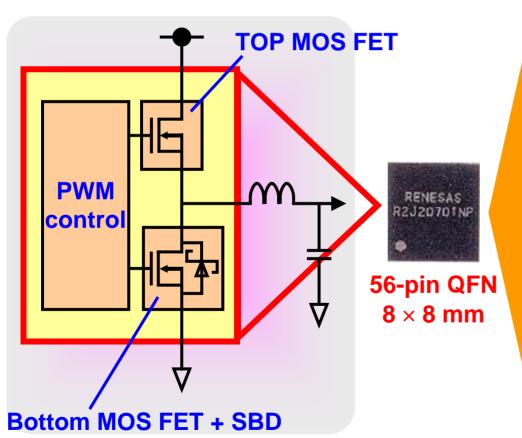
Sample system configuration: DC-DC power supply for DDR RAM



POL-SiP (R2J20702NP) (1)

PWM IC, MOS FET × 2 → Incorporated in a single package

Fully compatible with R2J20701NP pin assignment



Compact/space saving

57% cut in mounting area (compared to discrete devices)

Large current/
High power efficiency

High response speed

Multi-functionality

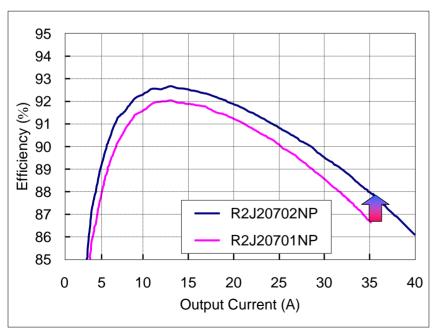
POL-SiP (R2J20702NP) (2)

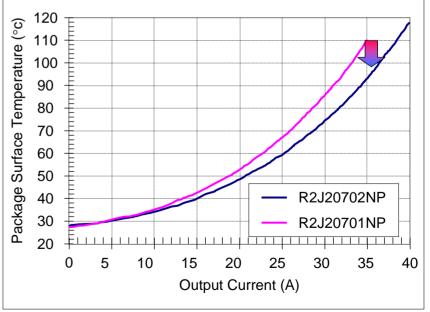
Low loss and high power efficiency keeps heat generation down.

Evaluation data

Efficiency + Package Surface Temperature

Test conditions $V_{IN} = 12 \text{ V}$, $V_{OUT} = 1.8 \text{ V}$, fsw = 500 kHz, $L = 0.32 \text{ }\mu\text{H}$, $C_{OUT} = 600 \text{ }\mu\text{F}$, no air flow



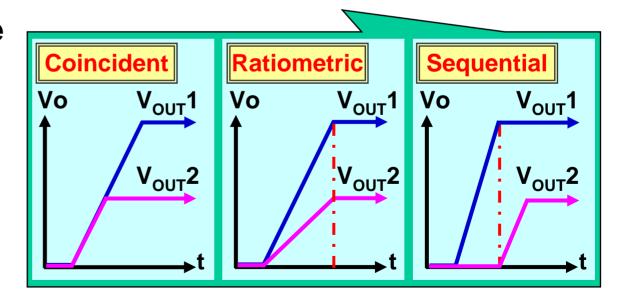


POL-SiP (R2J20702NP) (3)

Availability of various styles of parellel driving simplifies design.

- Large-current driving (80A)
- **Current sharing**
- **Automatic phase** shifting by 180°

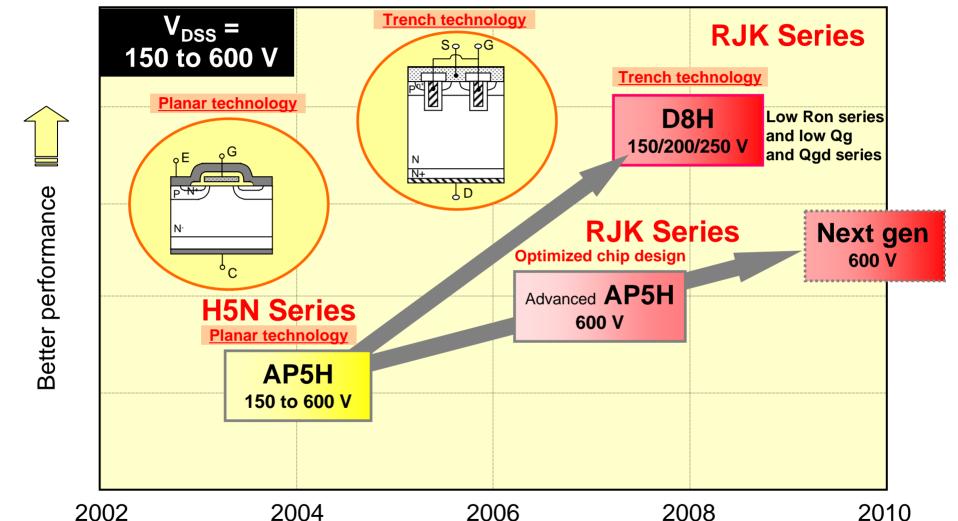
- 2-phase operation Multi-channel operation
 - Parallel synchronous behavior
 - Various kinds of tracking start are available.



Power MOS FETs

Medium-/High-Voltage Power MOS FETs $V_{DSS} = 150 \text{ V}$ to 600 V

Roadmap of Medium-/High-Voltage **Power MOS FETs**



Features of Medium-, High-Voltage Power MOS FETs

- Lineup of ultra-low on-resistance,
 large-current products
 - RJK2511DPK: 250 V, 65 A, 34 mΩ, TO-3P
 - RJK4018DPK: 400 V, 43 A, 100 mΩ, TO-3P
 - RJK5020DPK: 500 V, 40 A, 115 mΩ, TO-3P
 - RJK6020DPK: 600 V, 32 A, 175 mΩ, TO-3P
- Low gate charge (low Qg)
- Avalanche tolerance guaranteed
- Built-in diode with high breakdown-tolerance

New Products: 8th Generation Trench-type (150 V- 250 V)

New Products

Low on-state resistance

Low on-state resistance series

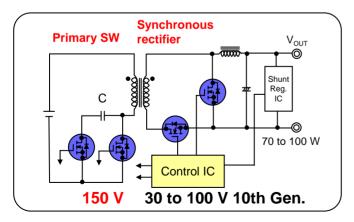
	Package	Part No.	V_{DSS}	I _D	R _{DS} (on)	Ciss	Qg	Qgd	Sche	edule
	rackage	Fait No.	[V]	[A]	Max. $[\Omega]$	Typ. [pF]	Typ. [nC]	Typ. [nC]	ES	MP
		RJK1555DPA	150	25	0.048	2400	38	10.2	OK	OK
١	WPAK	RJK2055DPA	200	20	0.069	2400	38	9.0	OK	OK
L		RJK2555DPA	250	17	0.104	2400	39	10.5	OK	OK

High speed switching

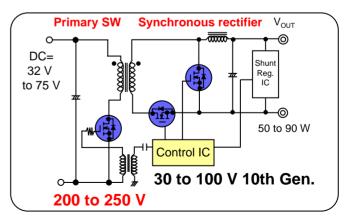
Low-Capacitance series

ſ	Package	Part No.	V_{DSS}	I _D	R _{DS} (on)	Ciss	Qg	Qgd	Sche	dule
	rackage	Fait No.	[V]	[A]	Max. $[\Omega]$	Typ. [pF]	Typ. [nC]	Typ. [nC]	ES	MP
I		RJK1557DPA	150	25	0.058	1250	20	5	OK	OK
ı	WPAK	RJK2057DPA	200	20	0.085	1250	19	5.3	OK	OK
L		RJK2557DPA	250	17	0.128	1250	20	5.9	OK	OK

Recommended application: primary-side switches of isolating brick converter



Active clamp circuit



Single-ended forward converter circuit

Lineup of 150- to 600-V Power MOS FETs (Compact Packages for Surface Mounting)

Packago	Part No.	\/ [\/]	Ι ΓΛ1	R _{DS} (on)	Ciss [pF]		nedule
Package	Part No.	V _{DSS} [V]	I _D [A]	R _{DS} (on) Max. [Ω]	Ciss [br]	WS	MP
	2SK4151	150	1	1.95	98	-	Available
TO-92	2SK4150	250	0.4	5.7	80	-	Available
10-92	HS54095	600	0.15	25	50	-	Available
	HS54097		0.2	16.5	66	-	Available
	2SK4093	250	1	2.6	140	-	Available
TO-92MOD	RJK6011DJE		0.1	52	25	-	Available
10-921000	RJK6022DJE	600	0.2	15	84	-	Available
	HS56021		0.2	15	84	-	Available
	RJK4006DPD	400	8	0.8	650	-	Available
	RJK5003DPD	500	5	1.5	550	-	Available
MP-3A	RJK5006DPD	300	7	1.3	650	-	Available
	RJK6002DPD		2	6.8	160	-	Available
(SMD)	RJK6023DPD	600	0.15	25	240	Available	Available
	RJK6024DPD		0.4	42	TBD	Available	Available
	RJK6025DPD		0.8	20	TBD	Available	Available
	RJK2006DPE	200	40	0.059	1800	-	Available
	RJK4012DPE	400	15	0.41	1120	-	Available
	RJK4013DPE	700	17	0.3	1470	-	Available
	RJK4512DPE	450	14	0.51	1100	-	Available
	RJK4513DPE	400	16	0.38	1440	-	Available
LDPAK-S	RJK5012DPE	500	12	0.62	1100	-	Available
(SMD)	RJK5013DPE	300	14	0.465	1470	-	Available
	RJK6026DPE		5	2.4	440	-	Available
	RJK6012DPE		10	0.92	1100	-	Available
	RJK6024DPE	600	0.4	42	TBD	Available	Available
	RJK6025DPE		8.0	20	TBD	Available	Available
	RJK6013DPE		11	0.7	1470	-	Available



TP-92



TP-92MOD



MP-3A

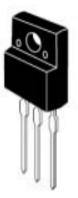


LDPAK-S

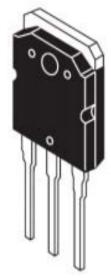
Lineup of 400- to 600-V Power MOS FETs (3-Pin Through-Hole Packages)

O	7	
		J
) 0-3		

5 .	D (N)	V _{DSS}	I _D	R _{DS} (on)	Ciss	Sche	edule
Package	Part No.	[V]	[A]	Max. [Ω]	[pF]	WS	MP
TO-220FN	RJK4007DPP	400	7.6	0.55	850	-	Available
(full mold)	RJK5026DPP	500	6	1.75	450	-	Available
,	RJK5012DPP]	12	0.62	1100	-	Available
	RJK5013DPP]	14	0.465	1470	-	Available
	RJK5014DPP]	19	0.38	1800	-	Available
	RJK5009DPP]	20	0.3	2600	-	Available
	RJK6026DPP	600	5	2.4	440	-	Available
	RJK6012DPP]	10	0.92	1100	-	Available
	RJK6013DPP]	11	0.7	1470	-	Available
	RJK6014DPP		16	0.575	1800	-	Available
TO-220FL	RJK6066DPP-MO		5	3	TBD	Available	'10/Q1
(full mold)	RJK6052DPP-MO]	10	1.15	TBD	Available	'10/Q1
,	RJK6053DPP-MO]	11	0.875	TBD	Available	'10/Q1
	RJK6054DPP-MO]	16	0.72	TBD	Available	'10/Q1
TO-3PFM	RJK2009DPM	200	40	0.036	2900	-	Available
	RJK5015DPM	500	25	0.24	2600	-	Available
	RJK6015DPM	600	21	0.36	2600	-	Available
TO-3P	RJK2508DPK	250	50	0.064	2600	-	Available
	RJK2511DPK]	65	0.034	4900	-	Available
	RJK4014DPK	400	24	0.24	1820	-	Available
	RJK4015DPK]	30	0.165	2600	-	Available
	RJK4018DPK		43	0.1	4100	-	Available
	RJK4514DPK	450	22	0.3	1820	-	Available
	RJK4515DPK		27	0.2	2600	-	Available
	RJK4518DPK		39	0.13	4100	-	Available
	RJK5013DPK	500	14	0.465	1470	-	Available
	RJK5014DPK		19	0.38	1800	-	Available
	RJK5015DPK		25	0.24	2600	-	Available
	RJK5018DPK]	35	0.155	4100	-	Available
	RJK5020DPK		40	0.118	5150	-	Available
	RJK6014DPK	600	16	0.575	1800	-	Available
	RJK6015DPK		21	0.36	2600	-	Available
	RJK6018DPK	1	30	0.235	4100	-	Available
	RJK6020DPK	1	32	0.175	5150	-	Available



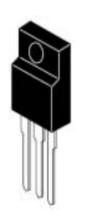
TO-220FN TO-220FL



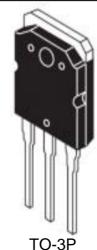
TO-3P

Lineup of 250- to 600-V Power MOS FET Products Incorporation High-Speed Diodes

Dookogo	Part No.	V _{DSS}	I _D	R _{DS} (on)	Ciss	Schedule		
Package	Fait No.	[V]	[A]	Max. [Ω]	[pF]	WS	MP	
TO-220CFM	H5N2512CF	250	18	0.105	2200	-	Available	
(full mold)	H5N3007CF	300	15	0.16	2180	-	Available	
TO-220FN	H5N2522FN	250	12	0.21	1300	-	Available	
(full mold)	RJL5012DPP	500	12	0.7	1050	-	Available	
	RJL5013DPP		14	0.51	1400	-	Available	
	RJL6012DPP	600	10	1.1	1050	-	Available	
	RJL6013DPP		11	0.81	1400	-	Available	
	RJL6014DPP		15	0.635	1680	-	Available	
TO-3P	H5N2507P	250	50	0.055	5000	-	Available	
	H5N3008P	300	40	0.069	5150	-	Available	
	RJL5020DPK	500	38	0.14	TBD	-	Available	
	RJL6020DPK	600	30	0.21	TBD	-	Available	







TO-220CFM TO-220FN

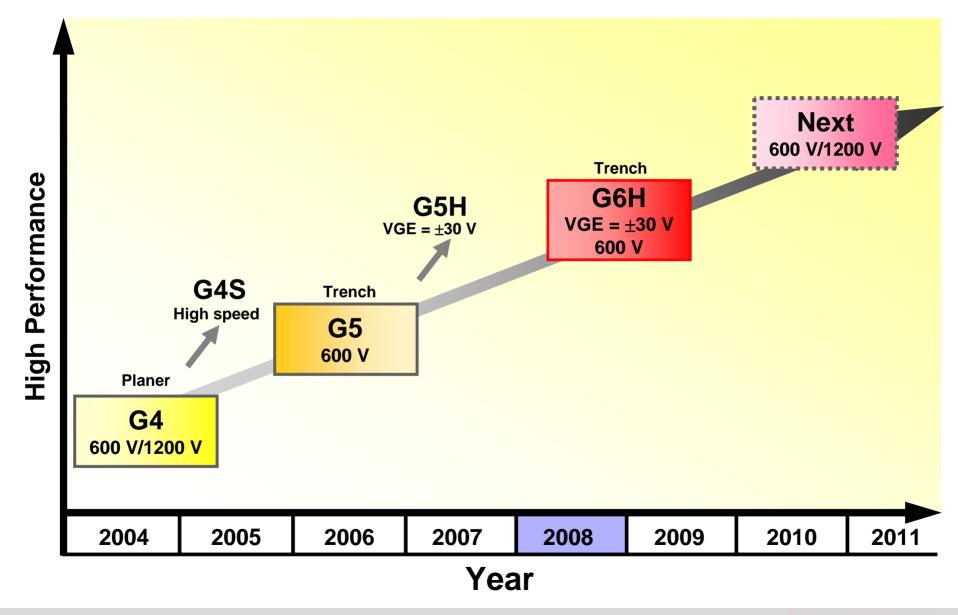
IGBT

- IGBTs for Industrial and HA Applications
- IGBTs for Strobe Flash

IGBT

IGBTs for Industrial and HA Applications

IGBT Road Map



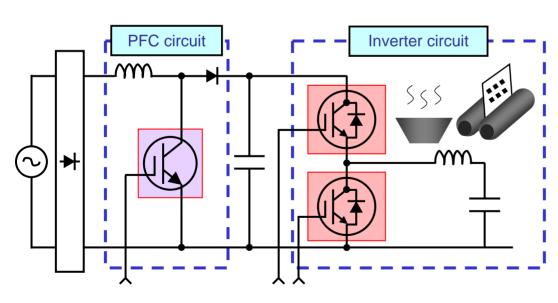
IGBTs for Cook Top

Features and Merits

Best support for miniaturization and high efficiency

Circuit	Family	Part No.	Feature	Merit			
current synchronous resonance circuit	Low V _{CE} (sat) High Speed type	RJH60F4DPK	Low saturation voltage High speed switching (90 ns) typ. Small package (TO-3P)	For high output, Low ON loss For high frequency, Low switching loss Miniaturization			

■ Circuit Examples (Half-bridge current synchronous resonance circuit)



IH: Induction Heating A method of pot heating by using electromagnetic induction, spiral current generate at the bottom of pot on heater.





TO-3P

Low V_{CE} (sat) High Speed IGBT Lineup

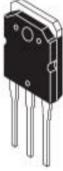


Features

- 600 V class products with Thin wafer and Trench technology
- Low Collector to Emitter saturation voltage V_{CE} (sat)
- Pb free (Lead dip and Chip bonding)

P/N	V _{CES} I _C		V _{CE (sat)}		tf	Dio	Dookogo	
F/IN	[V]	[A]	Typ. [V]	Conditions	Typ. [ns]	V _F typ. (V)	trr typ. (ns)	Package
RJH60F0DPK	600	50	1.40	$I_{\rm C} = 25 {\rm A}$	90	1.6	140	TO-3P
RJH60F4DPK	600	60	1.40	$I_{\rm C} = 30 {\rm A}$	80	1.6	140	TO-3P
RJH60F5DPK	600	80	1.37	$I_{\rm C} = 40 \ {\rm A}$	80	1.6	140	TO-3P
RJH60F6DPK	600	85	1.35	$I_{\rm C} = 45 \; {\rm A}$	95	1.6	140	TO-3P
RJH60F7ADPK	600	90	1.35	$I_{\rm C} = 50 \; {\rm A}$	95	1.6	140	TO-3P

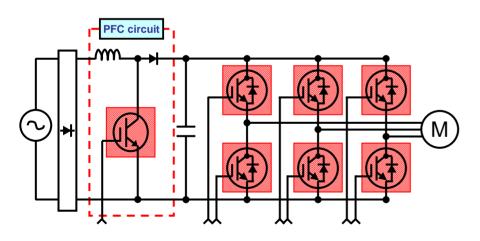
Development schedule plan							
WS	MP						
OK	′10/Q1						
OK	OK						
OK	OK						
OK	′10/Q1						
OK	OK						



TO-3P

IGBTs for Motor Control and Inverter Units

Device	Features	Merit			
	Low V _{CE} (sat) (1.6 V) typ.	Making to high power			
High Short circuit capability IGBT	Fast recovery diode (100 ns) typ.	Miniaturization			
	Short circuit capability 5 μs min.	High reliability			



Circuit example of Motor control

Applications

Air conditioner, Refrigerator, Washing machine Photovoltaic generation, UPS, Machine tool, Fan control, and general-purpose inverter unit etc.

High Short Circuit Capability IGBT Lineup





[tsc] Test condition: $V_{CE} = 400 \text{ V}$, $V_{GE} = 15 \text{ V/Tc} = 100^{\circ}\text{C}$

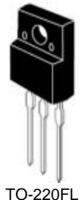
IGBT V _{CE}	V	1 (4)	V _{CE (sat)} (V)			tf (ns)			tsc (µs)	Built-in		Status	
		○ \	typ.	I _C (A)	V _{GE} (V)	typ.	I _C (A)	V _{CE} (V)	min.	FRD	Package	ws	MP
RJH60C9DPD	600	(10)/(5)	(1.9)	5	15	(100)	5	300	(5)	Yes	MP-3A	OK	'10/Q1
RJH60D1DPP	600	(16)/(8)	(1.6)	8	15	(100)	8	300	(5)	Yes	TO-220FL	OK	'10/Q1
RJH60D1DPE	600	(16)/(8)	(1.6)	8	15	(100)	8	300	(5)	Yes	LDPAK (S)	OK	'10/Q1
RJH60D2DPP	600	(20)/(10)	(1.6)	10	15	(100)	10	300	(5)	Yes	TO-220FL	OK	'10/Q1
RJH60D2DPE	600	(20)/(10)	(1.6)	10	15	(100)	10	300	(5)	Yes	LDPAK (S)	OK	'10/Q1
RJH60D3DPP	600	(30)/(15)	(1.6)	15	15	(100)	15	300	(5)	Yes	TO-220FL	OK	'10/Q1
RJH60D3DPE	600	(30)/(15)	(1.6)	15	15	(100)	15	300	(5)	Yes	LDPAK (S)	OK	'10/Q1
RJH60D0DPK	600	(40)/(20)	(1.6)	20	15	(100)	20	300	(5)	Yes	TO-3P	OK	'10/Q1
RJH60D5DPK	600	(60)/(30)	(1.6)	30	15	(100)	30	300	(5)	Yes	TO-3P	OK	'10/Q1
RJH60D6DPK	600	(80)/(40)	(1.6)	40	15	(100)	40	300	(5)	Yes	TO-3P	OK	'10/Q1
RJH60D7DPK	600	(90)/(50)	(1.6)	50	15	(100)	50	300	(5)	Yes	TO-3P	OK	'10/Q1

Applications

Solar photovoltaic system, air-conditioning, refrigerator, washing machine, UPS, Eco Cute and other.

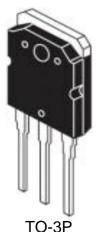


MP-3A





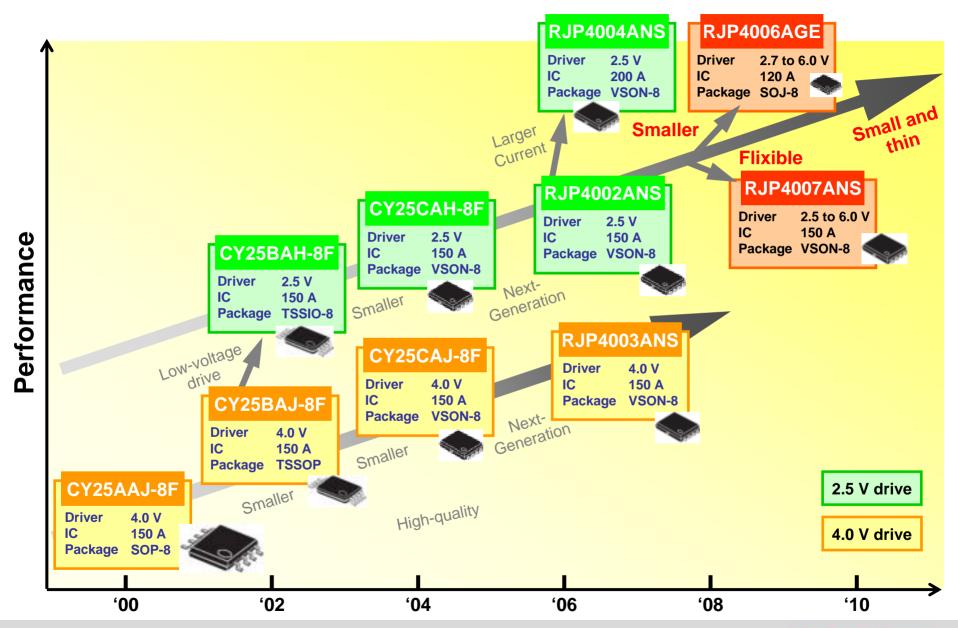
LDPAK-S



IGBT

IGBTs for Strobe Flash

Development Roadmap of IGBT for Strobe Use



Development of Products for Large-Current Control: IGBT for Internal Strobe Use



Part No.

RJP4004ANS

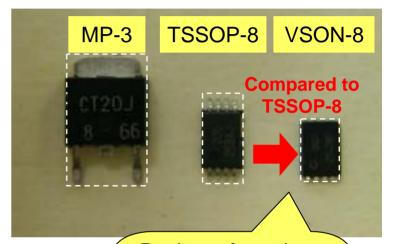
Features

- 1. Large current (200 A) Making possible more compact xenon tubes
- 2. Industry's smallest package (VSON-8: 3044)
- 3. Low-voltage drive (2.5 V) Optimized for 3.3-V power supply
- 4. High ESD level
- 5. Full lead-free



Development Product

Dowt No.	V _{CES}	I _{CP}	Drive	Doolsono	Schedule			
Part No.	[V]	[Å]	[V]	Package	WS	CS	MP	
RJP4004ANS	400	200	2.5 V	VSON-8	OK	OK	OK	



Package footprint: Reduced to 25% Package height:

New Products of IGBT for Strobe



Part No.

1. VSON-8 package: RJP4007ANS

2. SOJ-8 package: RJP4006AGE

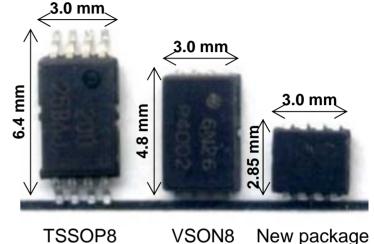
Features

1. Ultra small package (SOJ-8: size: 3.05 × 2.85 mm)

2. Flexible free (2.5 V (2.7 V) to 6.0 V)

3. High ESD capability (built-in gate zener diode)

4. Completed Pb Free and Halogen Free



TSSOP8 VSON8 New package SOJ8

Lineups

Dowt No.	V _{CES}	I _{CP}	Drive	Doolsogo	Schedule			
Part No.	[V]	[Å]	[V]	Package	WS	CS	MP	
RJP4006AGE	400	120	2.7 to 6.0 V	SOJ-8	OK	OK	OK	
RJP4007ANS	400	150	2.5 to 6.0 V	VSON-8	OK	OK	OK	

Lineup of Renesas IGBT for Strobe Use

	Ma	aximum ratii	ngs	
Part No.	V _{CES} [V]	I _{CP} [A]	Drive [V]	Package
CY20AAJ-8H (Note)	400	130	4.0	SOP-8
RJP4003ASA	400	150	4.0	TSSOP-8
RJP4002ASA	400	150	2.5	TSSOP-8
RJP4003ANS	400	150	4.0	VSON-8
RJP4002ANS	400	150	2.5	VSON-8
RJP4004ANS*	400	200	2.5	VSON-8
RJP4301APP* (Note)	400	200	30.0	TO-220FN
RJP5001APP* (Note)	400	300	12.0	TO-220FN
RJP4006AGE	400	120	2.7-4.0	SOJ-8
RJP4007ANS	400	150	2.5-4.0	VSON-8

*: Under Development (Note): High frequency type



Triacs and Thyristors

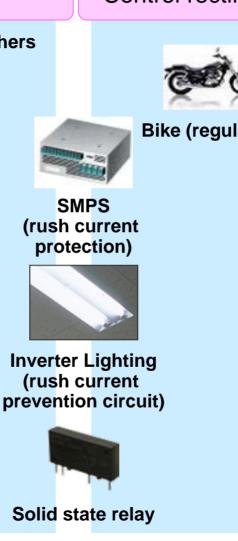


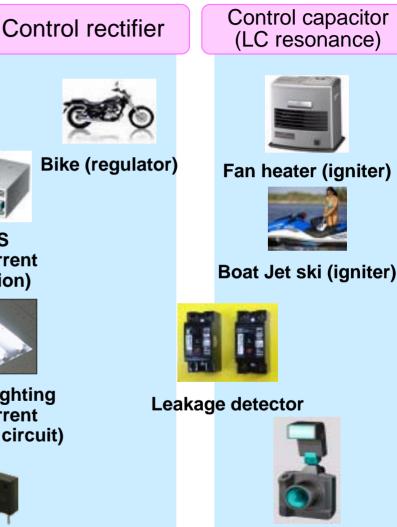
Examples of Thyristor and Triac Applications

Triacs Thyristors





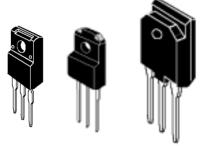




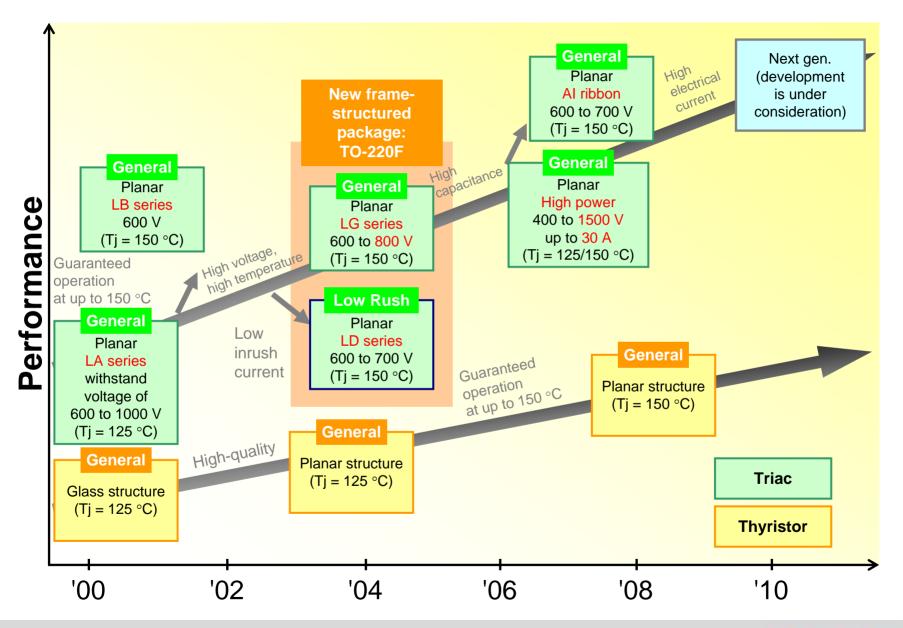
Camera (strobe)

Features of Renesas Thyristors and Triacs

- Development of guaranteed products against 150°C junction temperature (600 V/700 V/800 V)
 - LB/LC/LD/LG Series
- Abundant lineups of products
 - TO-220 full-mold type, UL certified
 - TO-3P full-mold type,
 for products requiring large current
 - Variety of lead-forming packages
- Product development optimized for applications
 - For applications for low-rush current • LC and LD Series, etc.
- Development of high-voltage products
 - 700 V, 800 V, 1000 V, 1500 V



Roadmap of Triac and Thyristor Development



Development of LG-Series Products: General-Purpose Triacs

Applications
 Control of heaters and motors used for laundry machines, vacuum cleaners, rice cookers, etc

Features

- 1) High reliability: Adoption of planar structure
- 2) Insulation-type outline: TO-220F(1), dielectric strength of 2000 V, UL certified
- 3) High-withstand voltage: 600 V, 700 V, 800 V
- 4) High temperature guaranteed: 150 °C assured
- 5) Products in lead-forming package available

Product List

Part No.	V_{DRMS}	I _{TRMS}	I _{TSM}	I _{GT} (max.)	Sta	itus	Note
rait No.	[V]	[A]	[A]	[mA]	CS	MP	Note
BCR3PM-12LG		3	30	20	OK	OK	_
BCR5PM-12LG	600	5	50	20	OK	OK	
BCR8PM-12LG		8	80	30	OK	OK	_
BCR10PM-12LG		10	100	30	OK	OK	_
BCR12PM-12LG		12	120	30	OK	OK	
BCR16PM-12LG		16	160	30	OK	OK	_
BCR3PM-14LG		3	30	20	OK	OK	
BCR5PM-14LG		5	50	30	OK	OK	Support V _{DRMS}
BCR8PM-14LG	700	8	80	30	OK	OK	= 800 V
BCR12PM-14LG	-	12	120	30	OK	OK	(@Tj = 125°C)
BCR16PM-14LG		16	160	30	OK	OK	
BCR8PM-16LG	800	8	80	30	OK	OK	<u> </u>



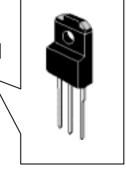
Development of LD-Series Products: Triacs for Low-Rush Current

Applications
 Low-rush current applications for ceramic heaters, etc.

Features

- 1) High reliability: Adoption of planar structure
- 2) Insulation-type outline: TO-220F(1), dielectric strength of 2000 V, UL certified
- 3) High-temperature guaranteed: 150 °C assured
- 4) High-noise tolerance: I_{GT} ≤ 50 mA
- 5) Products in lead-forming package available
- Product List

Dowt No.	Part No. V _{DRMS} I _{TRMS} I _{TSM}		I _{TSM}	I _{GT} (max.)	Status		
Part No.	[V]	[A]	[A] [mA]		CS	MP	
BCR8PM-12LD	000	8	48	50	OK	OK	
BCR10PM-12LD		10	60	50	OK	OK	
BCR12PM-12LD	600	12	72	50	OK	OK	
BCR16PM-12LD		16	96	50	OK	OK	
BCR5PM-14LD	700	5	30	50	OK	OK	
BCR8PM-14LD		8	48	50	OK	OK	



Development of High-Voltage and High-Capacity Triacs for General Purposes

Applications
 Rush-current protection circuit during power-on, heater control, motor control

Features

1) High reliability: Adoption of planar structure

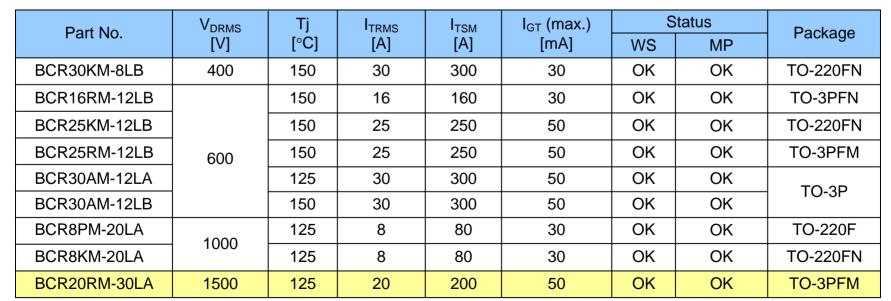
2) Insulation-type outline: TO-220F/TO-220FN/TO-3P/TO-3PF

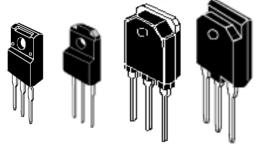
3) High-withstand voltage: 1000 V, 1500 V

4) Large current: 25 A/30 A at TO-220FN

5) Products in lead-forming package available







Development of High-Capacity Thyristors for General Purposes

Applications
 Rush-current protection circuit during power-on, inverters, etc.

Features

1) High reliability: Adoption of planar structure

2) Insulation-type outline: TO-220FN/TO-3PF/TO-220

3) Large current: 12 A/25 A

4) Products in lead-forming package available

5) Junction temperature guaranteed: 150 °C (-12B, -12D)







Product List

Part No.	V _{DRMS}	Tj	I _T (AV)	I _{TSM}	I _{GT} (max.)	Sta	tus	Package
i ait ivo.	[V]	[°C]	[A]	[A]	[mA]	WS	MP	1 donago
CR6PM-12A/12B		125/150	6	90	10	OK	OK	TO-220F
CR6CM-12A/12B		125/150	6	90	10	OK	OK	TO-220
CR8PM-12A/12B		125/150	8	120	15	OK	OK	TO-220F
CR8CM-12A/12B	600	125/150	8	120	15	OK	OK	TO-220
CR12PM-12A/12B		125/150	12	360	30	OK	OK	TO-220F
CR12CM-12A/12B		125/150	12	360	30	OK	OK	TO-220
CR25RM-12D		125	25	360	30	OK	OK	TO-3PFM

125°C Guaranteed Triac Lineup

TO-220 package

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR5AM-12LA	5	50	600	720	20
BCR6AM-12LA	6	60	600	720	30
BCR8CM-12LA	8	80	600	720	30
BCR10CM-12LA	10	100	600	720	30
BCR12CM-12LA	12	120	600	720	30
BCR16CM-12LA	16	170	600	720	30
BCR20AM-12LA	20	200	600	720	30

TO-220FN package

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR3KM-12LA	3	30	600	720	20
BCR5KM-12LA	5	50	600	720	20
BCR8KM-12LA	8	80	600	720	30
BCR10KM-12LA	10	100	600	720	30
BCR12KM-12LA	12	120	600	720	30
BCR16KM-12LA	16	160	600	720	30
BCR20KM-12LA	20	200	600	720	30
BCR3KM-14LA	3	30	700	840	30
BCR5KM-14LA	5	50	700	840	30
BCR8KM-14LA	8	80	700	840	30
BCR12KM-14LA	12	120	700	840	30
BCR8KM-16LA	8	80	800	960	30
BCR8KM-20LA	8	80	1000	1200	30

TO-220F package (resistance load)

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR2PM-12RA	2	10	600	720	10 (2, 3)

TO-220FN package (resistance load)

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR3KM-12RA	3	30	600	720	15
BCR5KM-12RA	5	50	600	720	15

MP-3A/DPAK (L) package

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR3AS-12LA	3	30	600	720	15
BCR5AS-12LA	5	50	600	720	30

TO-220S package

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR8CS-12LA	8	80	600	720	30
BCR10CS-12LA	10	100	600	720	30
BCR12CS-12LA	12	120	600	720	30
BCR16CS-12LA	16	170	600	720	30

TO-92 package

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR08AM-12A	0.8	8	600	720	5 (2, 3)
BCR1AM-12	1	10	600	720	5 (4 = 10)
BCR1AM-12A	1	10	600	720	7 (1, 2, 3)
BCR08AM-14	0.8	8	700	840	5 (2, 3)

UPAK package

Part No.	I _{T (RMS)} (A)	I _{TSM} (A)	V _{DRM} (V)	V _{DSM} (V)	I _{GT} (mA)
BCR08AS-12A	0.8	8	600	720	5 (4 = 10)

Thyristor Lineup

MP-3A/DPAK (L) package

Part No.	I _{T (AV)} (A)	I _{TSM} (A)	V _{DRM} (V)	I _{GT} (mA)	V _{GT} (V)
CR3AS-12	3	90	600	0.1	0.8
CR5AS-12	5	90	600	0.1	0.8

MPAK package

Part No.	I _{T (AV)} (A)	I _{TSM} (A)	V _{DRM} (V)	I _{GT} (mA)	V _{GТ} (V)
CR05BS-8	0.1	10	400	0.1	0.8

UPAK package

Part No.	I _{T (AV)} (A)	I _{TSM} (A)	V _{DRM} (V)	I _{GT} (mA)	V _{GT} (V)
CR05AS-8	0.5	10	400	0.1	0.8
CR08AS-12	0.8	10	600	0.1	0.8

TO-220 package

Part No.	I _{T (AV)} (A)	I _{TSM} (A)	V _{DRM} (V)	I _{GT} (mA)	V _{GT} (V)
CR12CM-12	12	360	600	30	1.5

TO-92 package

Part No.	I _{T (AV)} (A)	I _{TSM} (A)	V _{DRM} (V)	I _{GT} (mA)	V _{GT} (V)
CR02AM-8	0.3	10	400	0.1	0.8
CR03AM-12	0.3	20	600	0.1	0.8
CR05AM-12	0.3	10	600	0.1	0.8
CR04AM-12	0.4	10	600	0.1	0.8
CR03AM-16	0.3	20	800	0.1	0.8
CR05AM-16	0.3	10	800	0.1	0.8

TO-220FN package

Part No.	I _{T (AV)} (A)	I _{TSM} (A)	V _{DRM} (V)	I _{GT} (mA)	V _{GT} (V)
CR3KM-12	3	70	600	0.1	0.8
CR6KM-12	6	90	600	10	1.0
CR8KM-12	8	120	600	15	1.0

Renesas Power MOS FETs, IGBTs, Triacs, and Thyristors General Presentation

Publication Date: Rev.1.00, July 2003

Rev.27.01, Feb 2, 2010

Published by: Sales Strategic Planning Div.

Renesas Technology Corp.

Edited by: Customer Support Department

Global Strategic Communication Div.

Renesas Solutions Corp.

©2010. Renesas Technology Corp. All rights reserved. Printed in Japan REJ13G0003-2701





Renesas Technology Corp.

©2010. Renesas Technology Corp., All rights reserved.

Renesas Power MOS FETs, IGBTs, Triacs and Thyristors General Presentation

